

Stato della produzione, installazione e test diamanti

Belle II - Italia
Pisa - November 22, 2017

Chiara La Licata - INFN & Univ. Trieste

Phase 2: 8 “PXD” diamond sensors

Phase 3: 8 “PXD” + 12 “SVD” diamond sensors

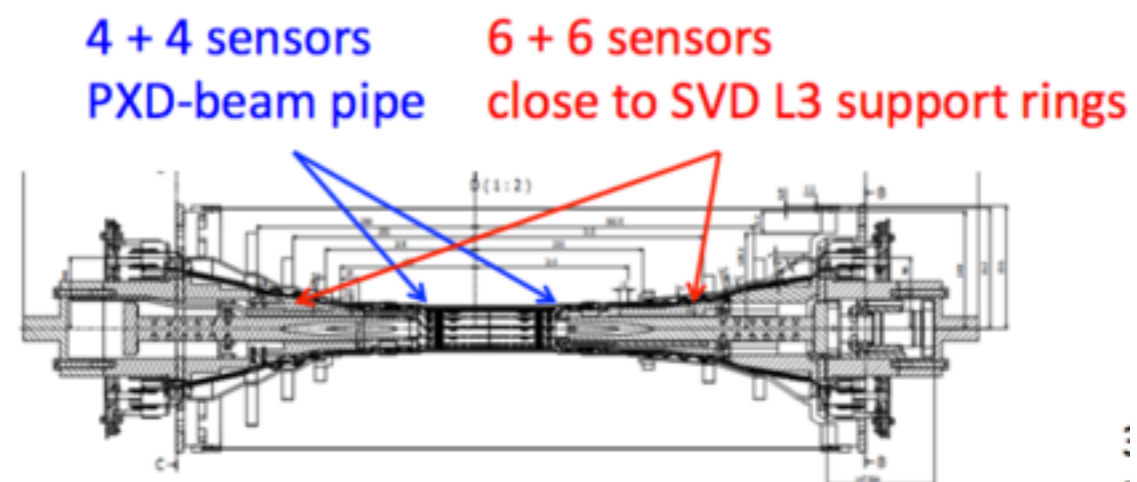
} in parallel

Diamonds assembly and testing

24 diamonds mounted on the final support.

23 fully tested:

- 14 already installed
- 9 almost ready for next installations



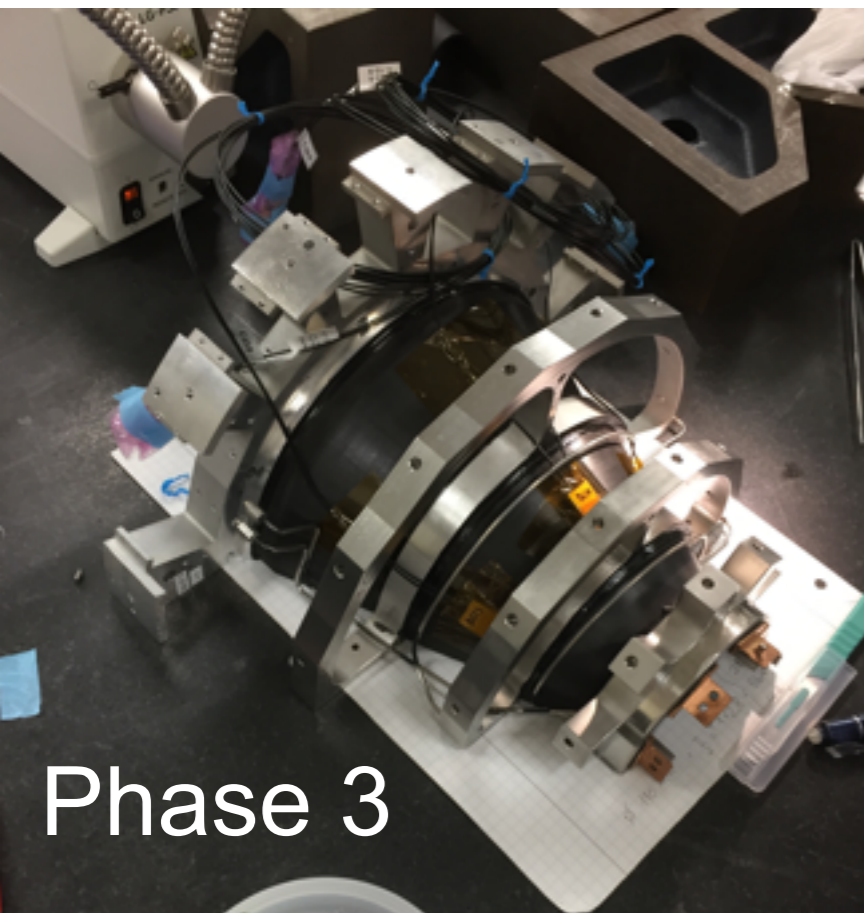
Schedule (only phase 3)

- 6 diamonds are needed for -X SVD half Ladder Mount and will be installed on December 01-16
- 8 more needed for Phase 3 for next year

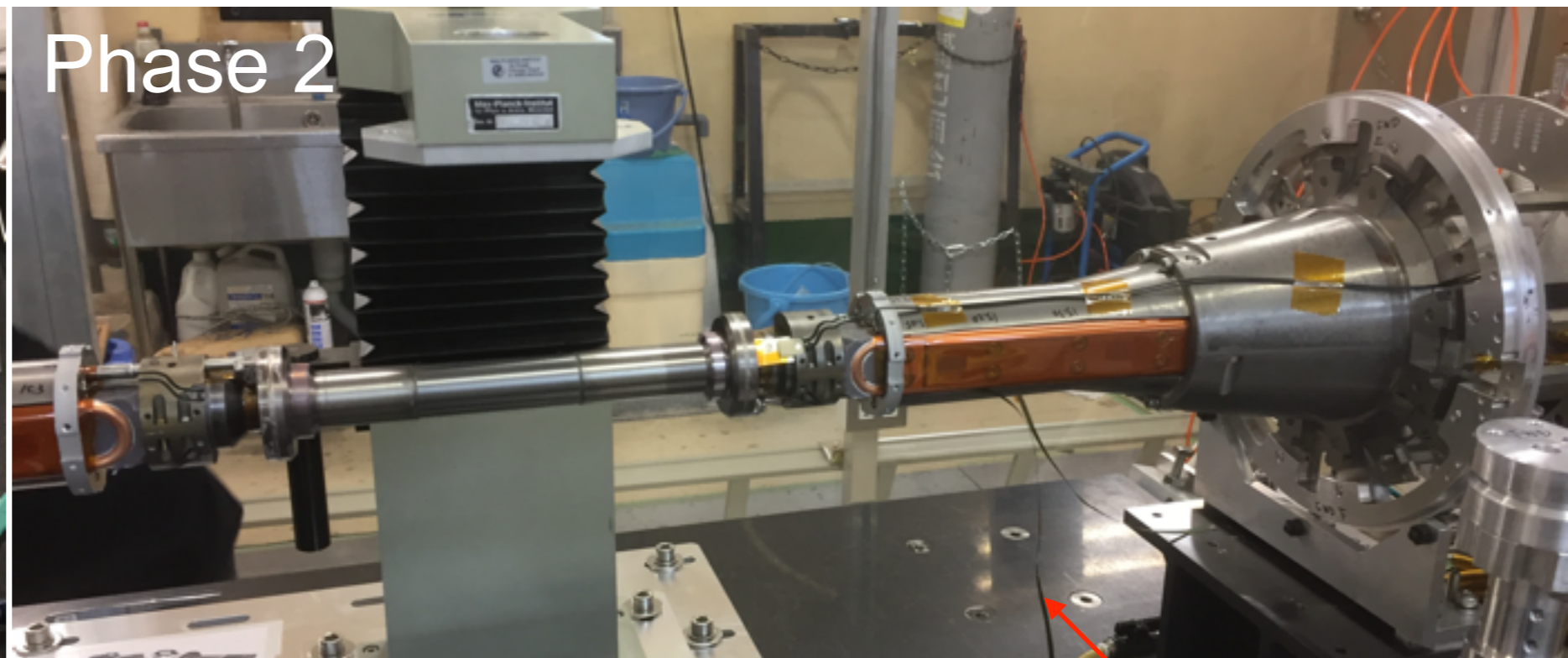
Other activity

- Irradiation tests of diamond sensors for a calibration with γ from ^{60}Co

Already installed



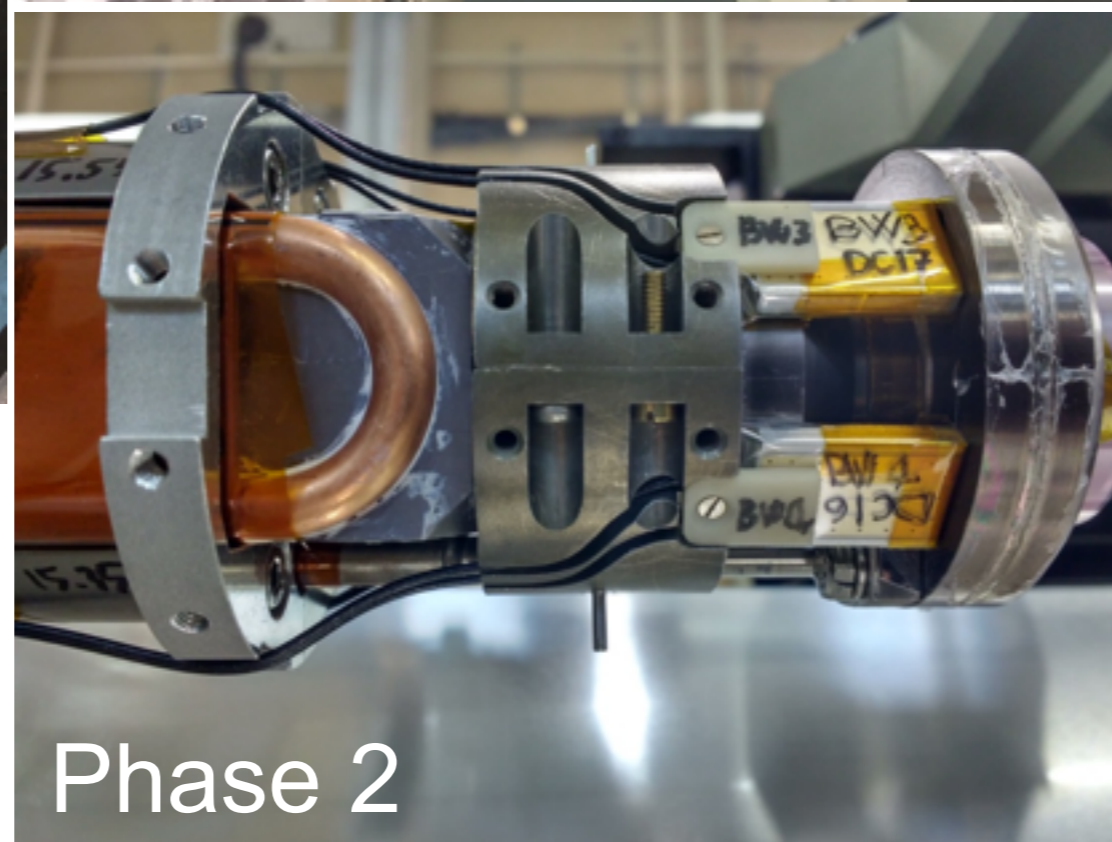
Phase 3



Phase 2

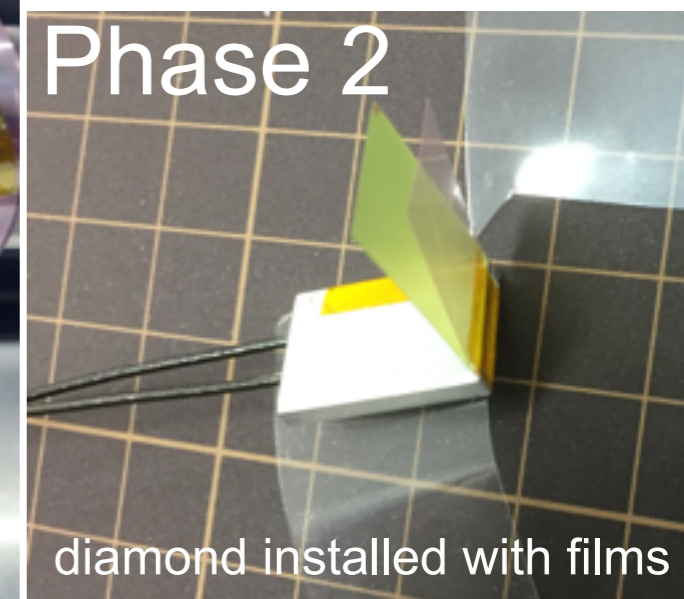


6 diamonds for +X SVD
(June 2017)



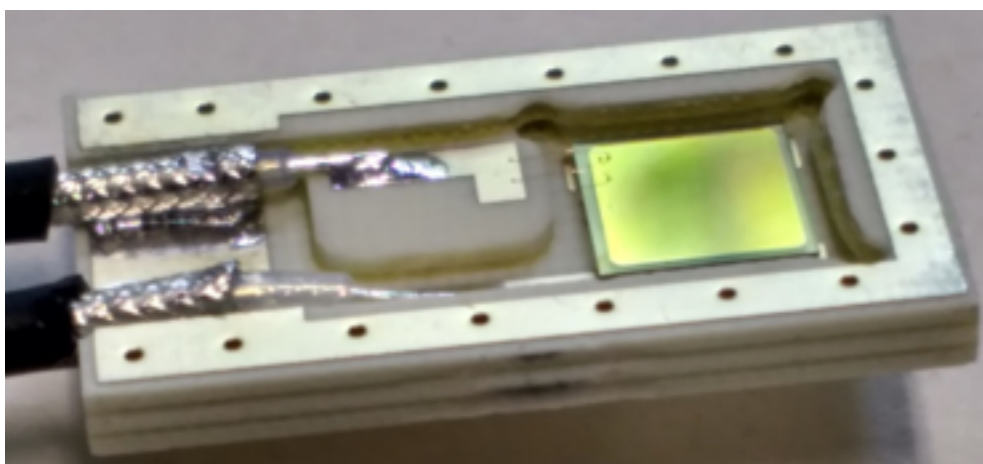
Phase 2

8 diamonds on the
beam pipe (Sept 2017)



Phase 2

diamond installed with films



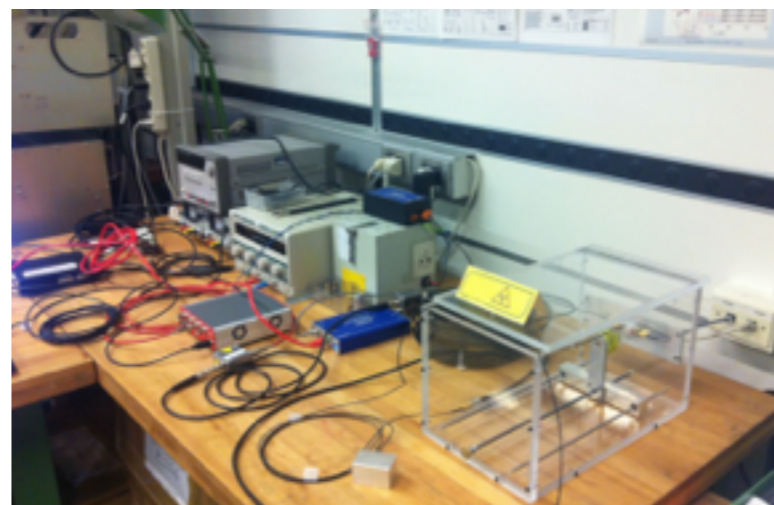
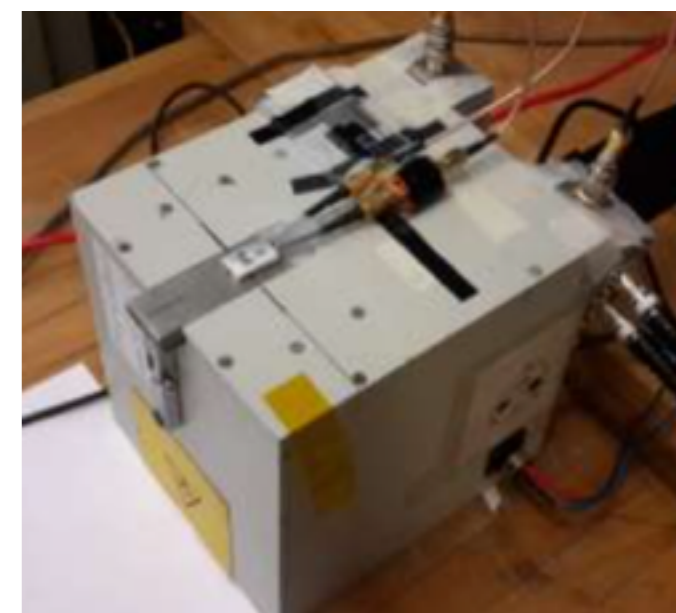
- the metallized diamond crystal is first glued on the printed circuit support

- the upper electrode is wire bonded

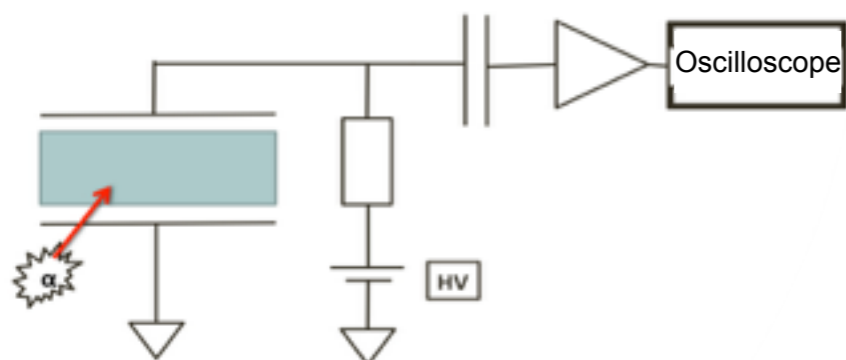
(0) Preliminary test: dark I-V characteristic:

Dark currents below the pA range at typical O(100V) operation voltage

- uniformity of electric field
- charge collection efficiency
- stability with time
- conversion from current to dose rate



(TCT = Transient Current Technique) α source: ^{241}Am , 55kBq

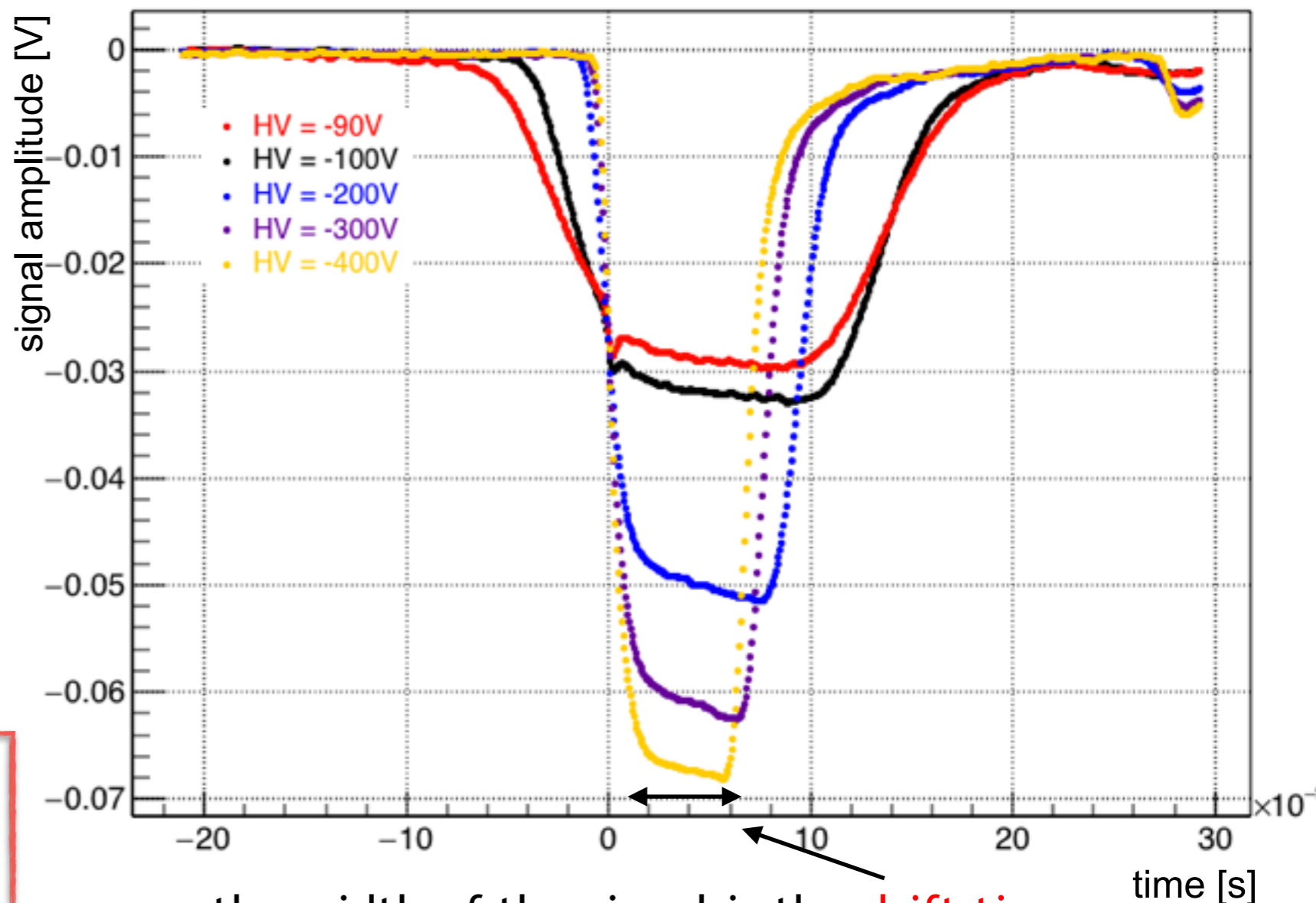


square pulse \rightarrow

check of the uniformity of the electric field in the diamond bulk

pulse area constant from -90V up to -400V

\rightarrow Fully efficient from -90V (CCE ~ 100%)

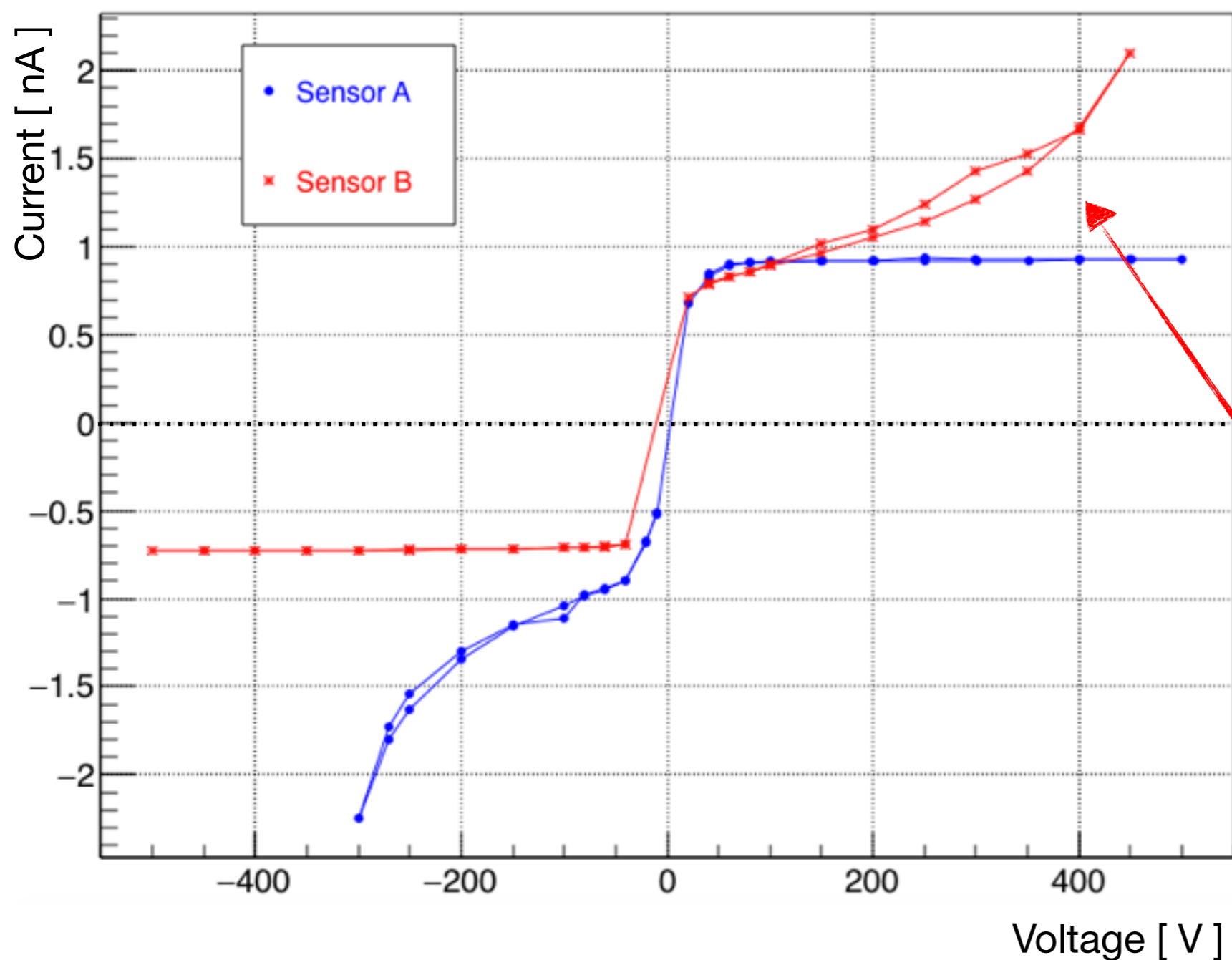


the width of the signal is the **drift time** (about 10ns) of charge carrier

it decreases consistently with the bias applied

I-V characteristic (just an example - typical behaviour)

2 single crystal CVD diamonds with metalization (Ti + Pt + Au)



source-sensor distance fixed at 2mm

Different behaviour observed for each diamond sensor

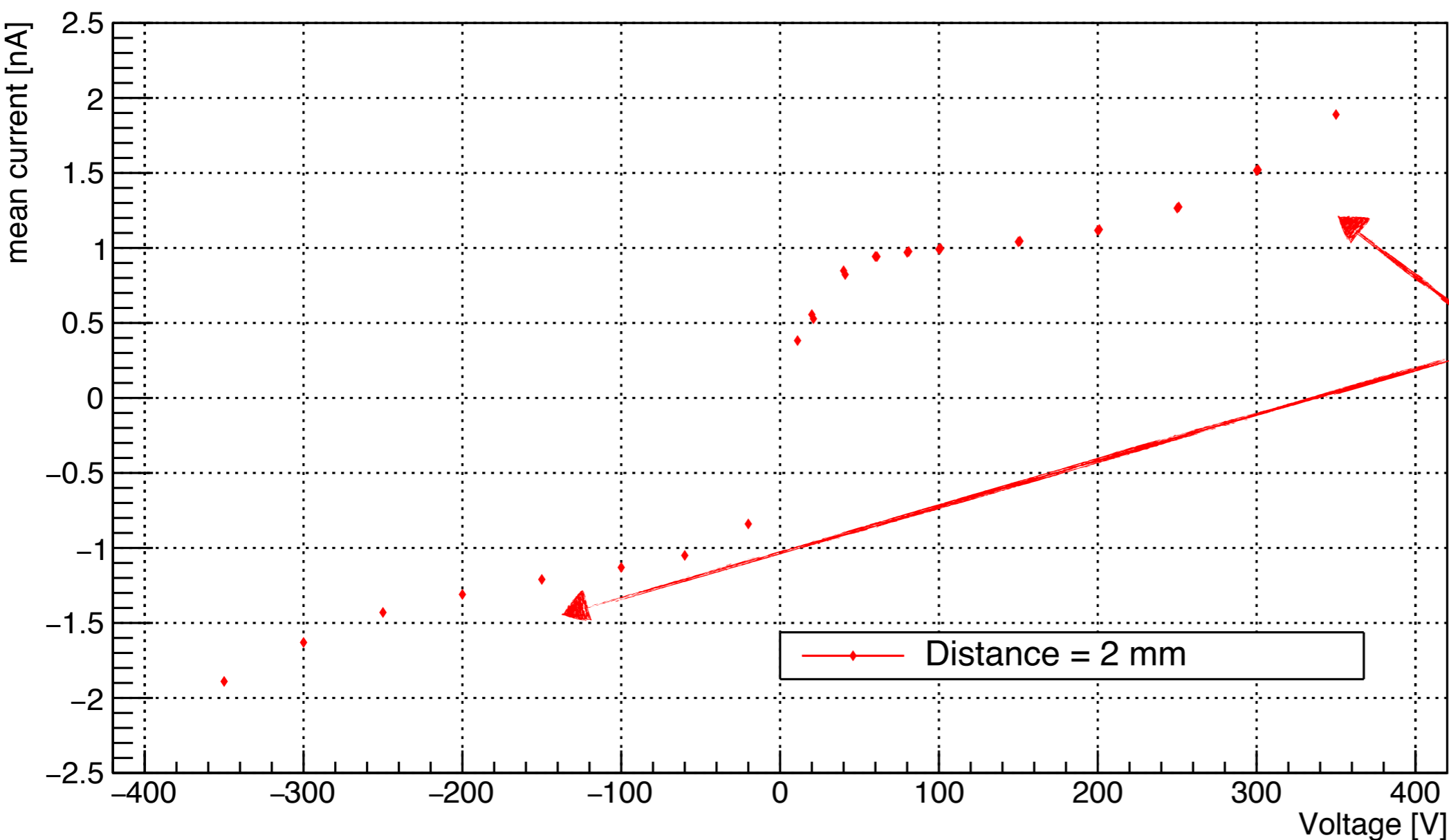
hysteresis loop in some sensors

deep levels act as centres to capture or emit carriers during the charging or discharging process

I-V characteristic (just an example - different behaviour)

2 single crystal CVD diamonds with metallization (Ti + Pt + Au)

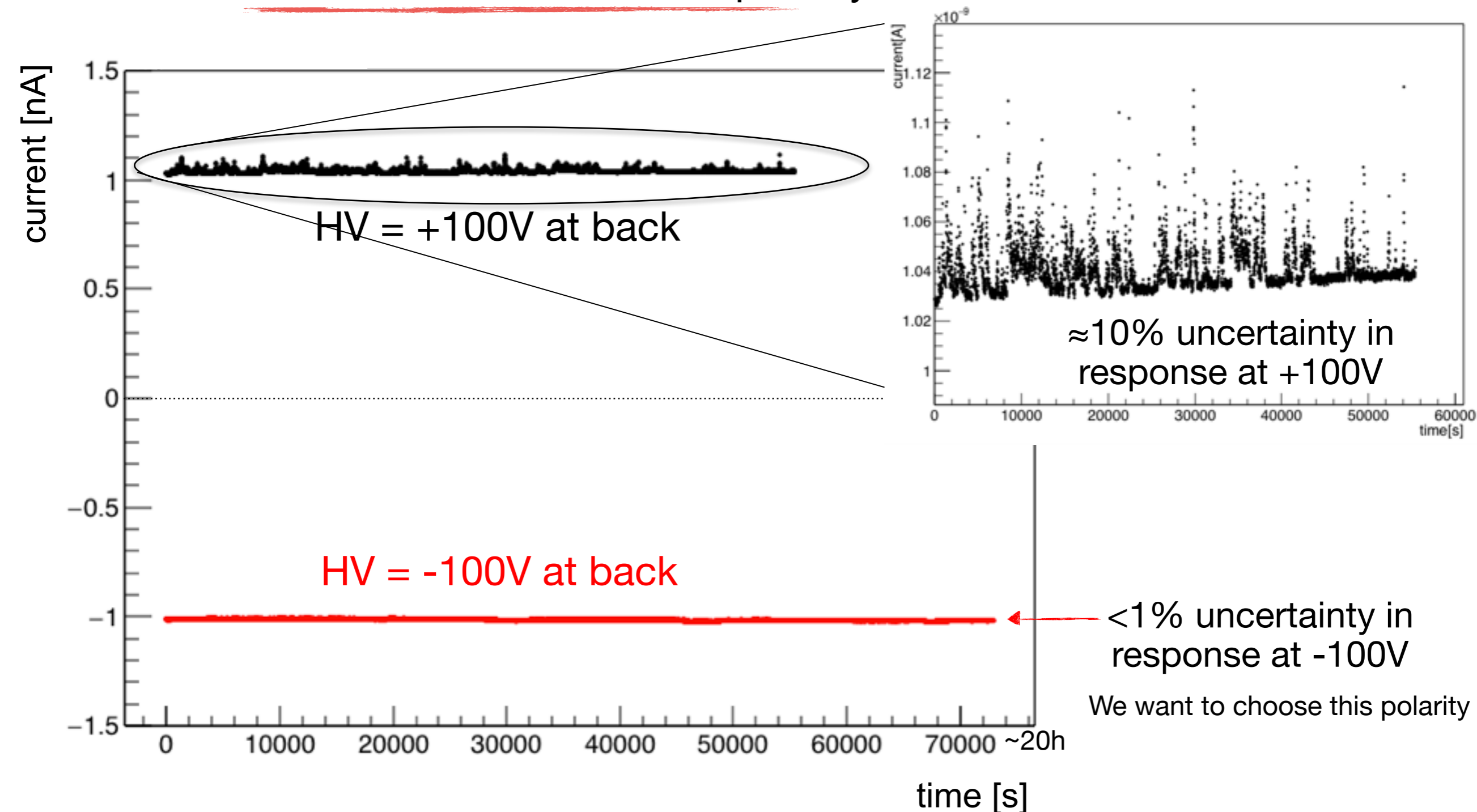
source-sensor distance fixed at 2mm



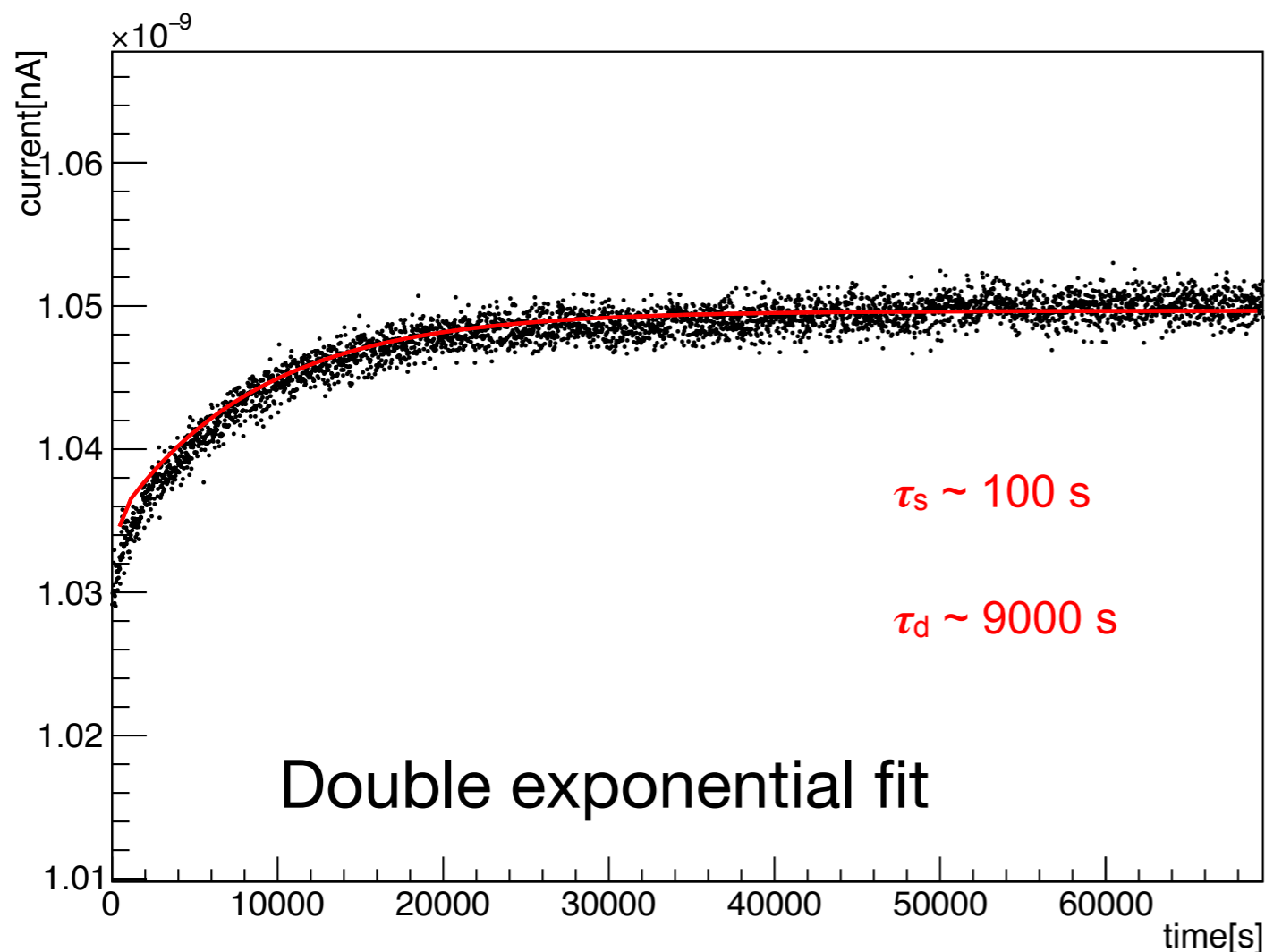
more symmetric trend, only short plateau

Check stability as diamonds will record dose for years

same diamond with different polarity



Transient



stability is reached after a transient

→ presumably due to traps in the crystal

Asymptotic state: both shallow and deep levels completely filled

Shockley-Hall-Read theory for impurity levels as trapping centres.

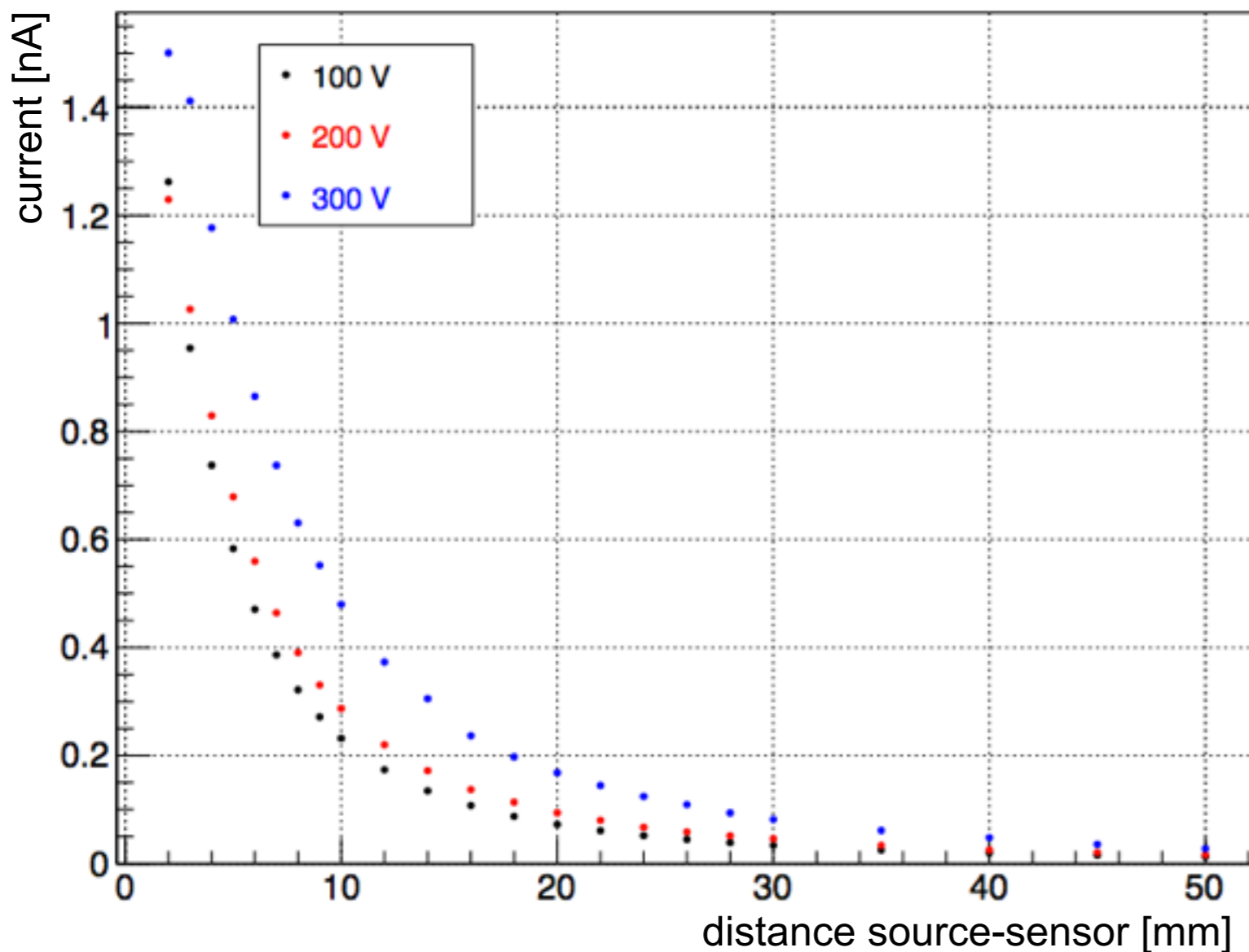
Two different types of traps:

- shallow traps
- deep traps

τ_s → time constant associated to shallow traps

τ_d → time constant associated to deep traps

inferred from the fit

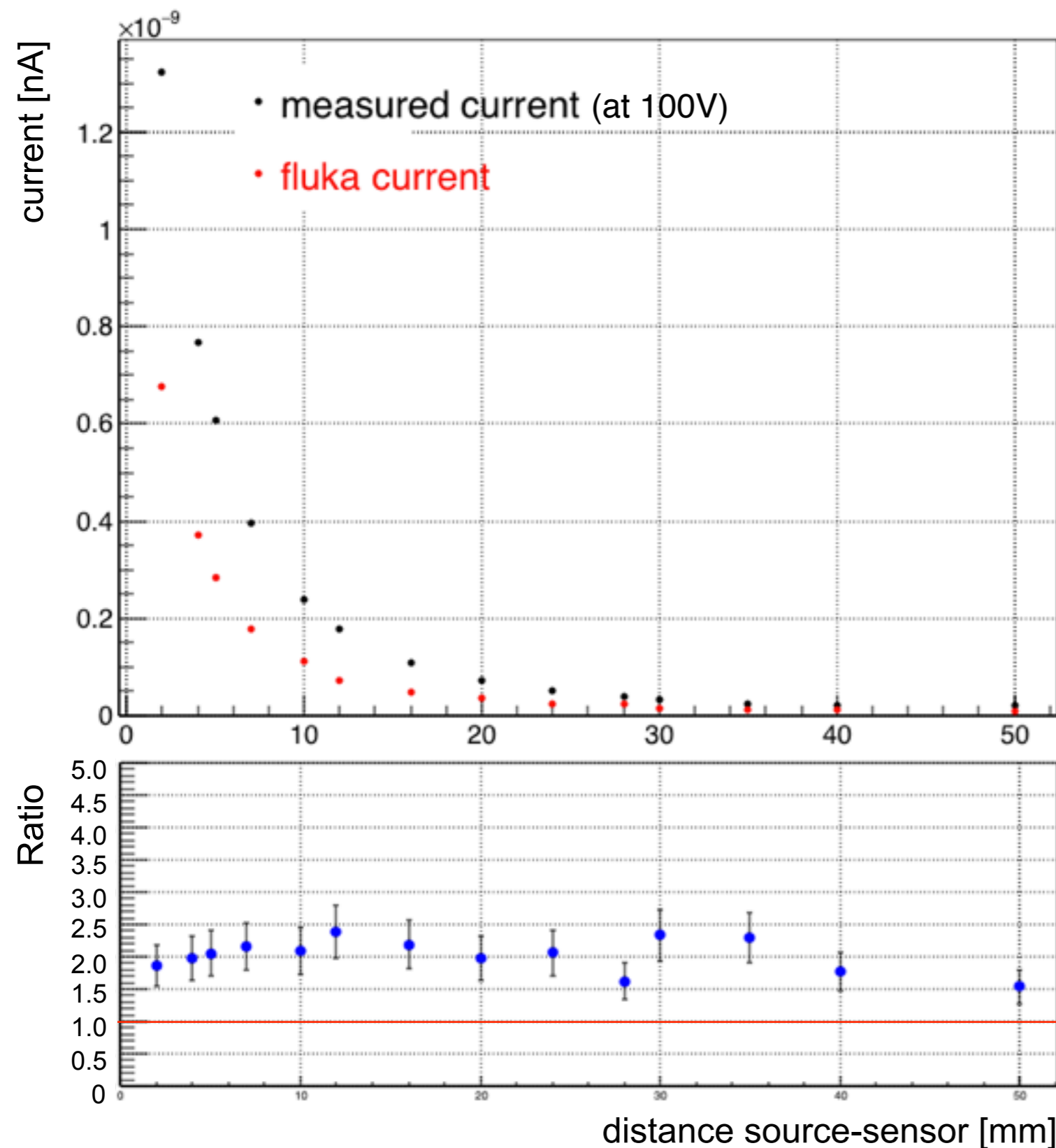


Response as a function of the distance between the source and the sensor depends on HV bias

→ photoconductive gain
 due to ohmic contact between electrodes and diamond → charge injected from the electrode

current-to-dose conversion requires knowledge of the photoconductive gain

Use FLUKA to compare with measurement and infer the gain for each diamond



current decreases approximately with the inverse square of the distance

→ agreement with simulation

measured current > simulated current

→ photoconductive gain (at 100V)

photoconductive gain

$$= I_{\text{meas}}/I_{\text{FLUKA}}$$

Systematic Uncertainty (phase 1)

$\delta G/G$ [%]

Source - Diamond sensor distance

10

Diamond sensor active volume

10

Diamond sensor priming or pumping

5

Source activity

7

FLUKA simulation statistics

1

HV reproducibility

1

Combination in quadrature

17

DONE

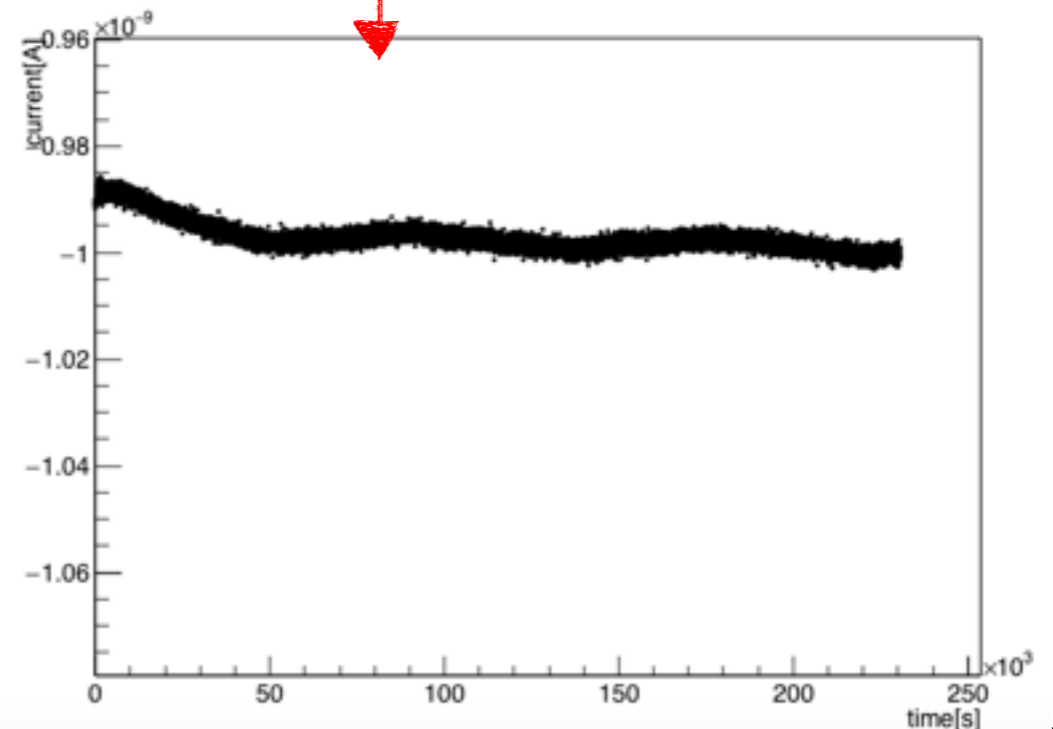
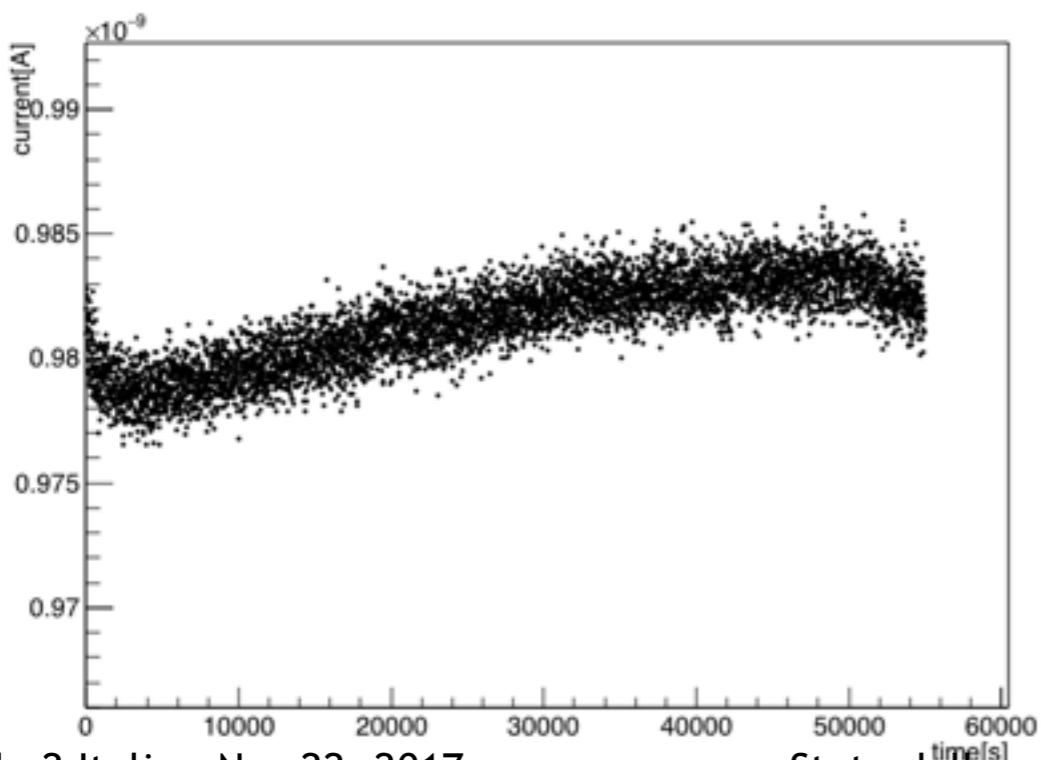
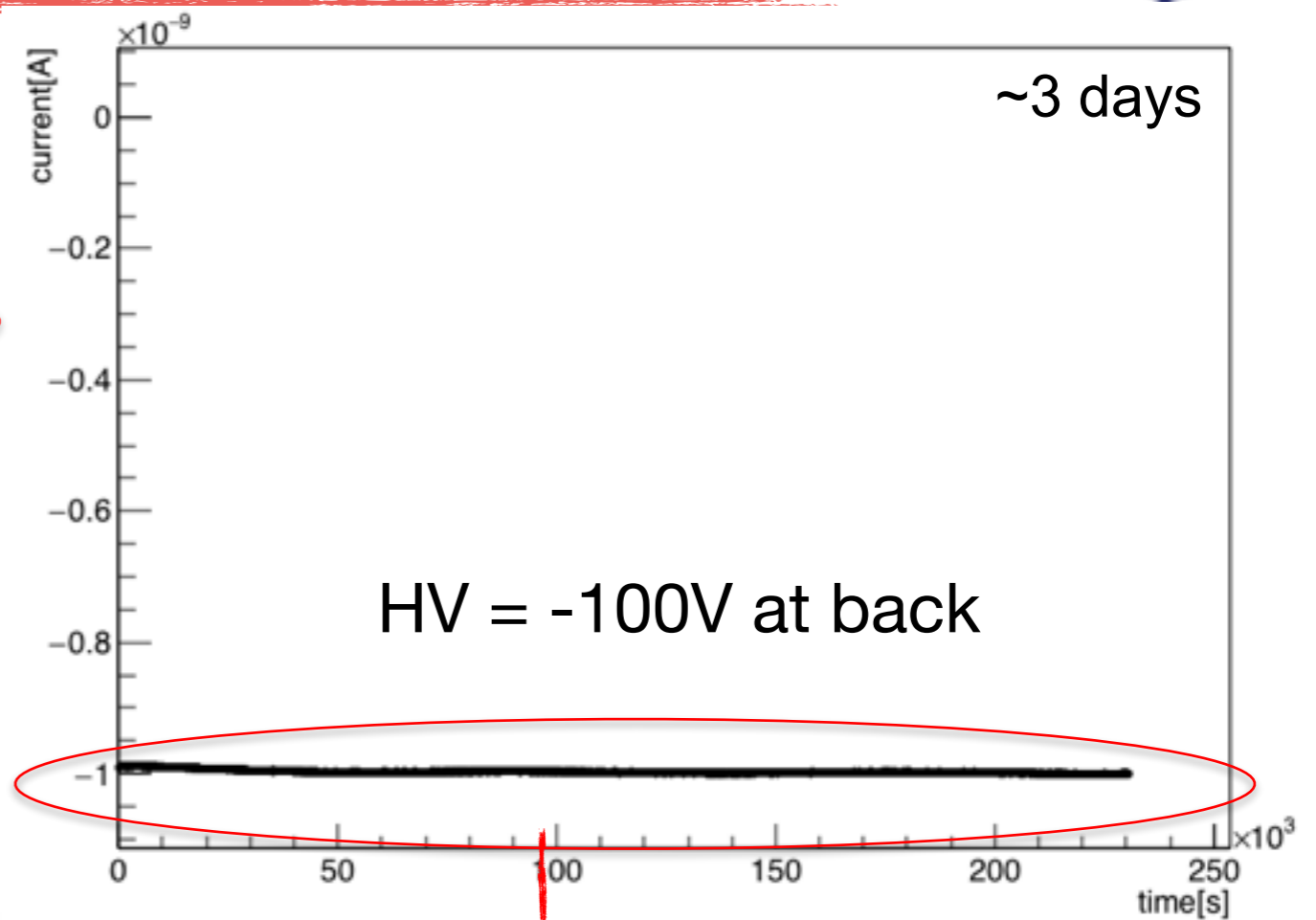
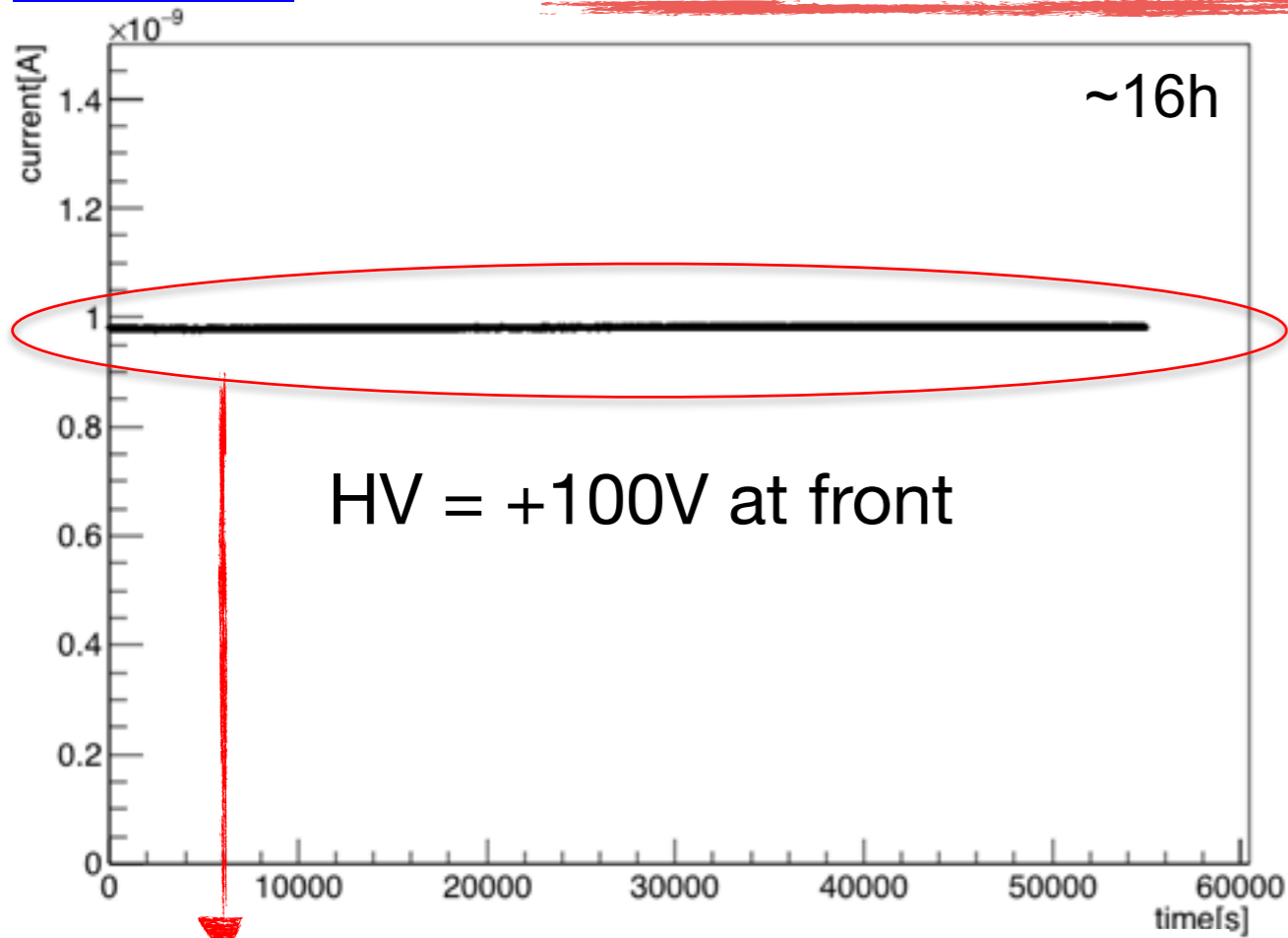
- Installation of 8 diamond sensors for phase 2
- Installation of 6 +X SVD diamond sensors for phase 3
- Installation of 6 -X SVD diamond sensors for phase 3
 - December 2017
- Installation of 8 “PXD” diamond sensors for phase 3
 - next year
- Tests on diamond sensors go on, the last 8 diamonds calibrated ready for the beginning of the next year
- Irradiation tests: first next week.



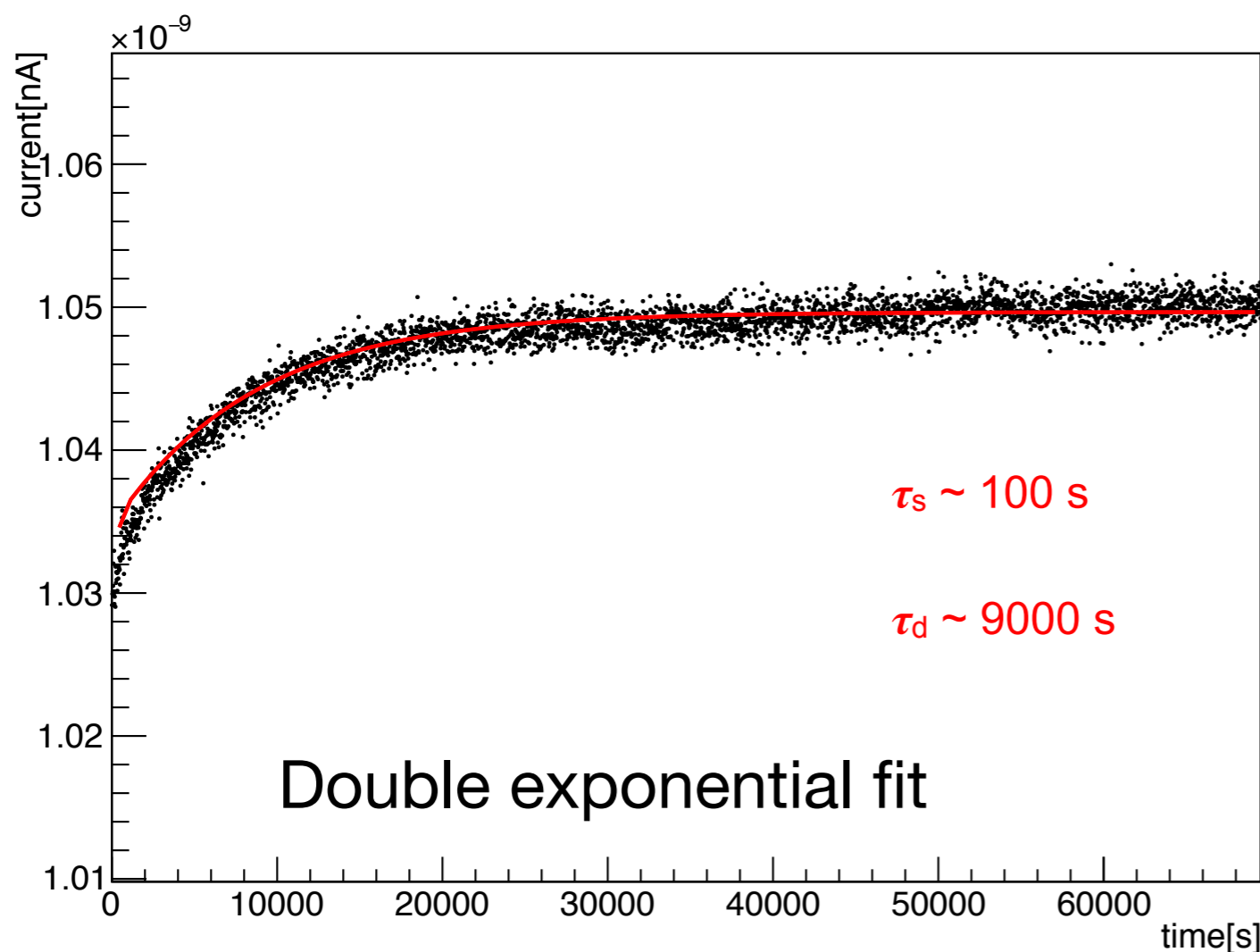
BACKUP

Specification	Value
Number of radiation sensors	20
diamond sensor size	5 mm×5 mm×500μm
maximum coax. cable length from sensor to electronics	3 + 40 m
sensor current/dose rate conversion factor	1 ÷ 10 nA/(mrad/s)
sensor current measurement sensitivity	0.01nA
sensor current measurement range	1 ÷ 10mA
normal frequency of current sampling	100 kHz
depth of buffer memory for specific events (aborts etc)	600 ms
normal frequency of data recording on slow control DAQ	1 ÷ 10 Hz
response time of fastest (hardware) beam abort trigger	10μs
response time of slow (software) beam abort trigger	> 10 s
instantaneous dose rate sensitivity	1.0 mrad/s
integrated dose overall relative uncertainty	5%
for typical diamond sensors (fast aborts):	Value
current measurement, precision (time scale 1 ms)	10 nA
response time	up to 10 μs
current range	0 ÷ 5 mA
for typical diamond sensors (slow aborts):	Value
current measurement, precision (time scale 1 s)	< 1 nA
response time	> 1 ÷ 100 s
current range	0 ÷ 15 μA

Stability



Transient



stability is reached after a transient

→ presumably due to traps in the crystal

Asymptotic state: both shallow and deep levels completely filled

Shockley-Hall-Read theory for impurity levels as trapping centres.

Two different types of traps:

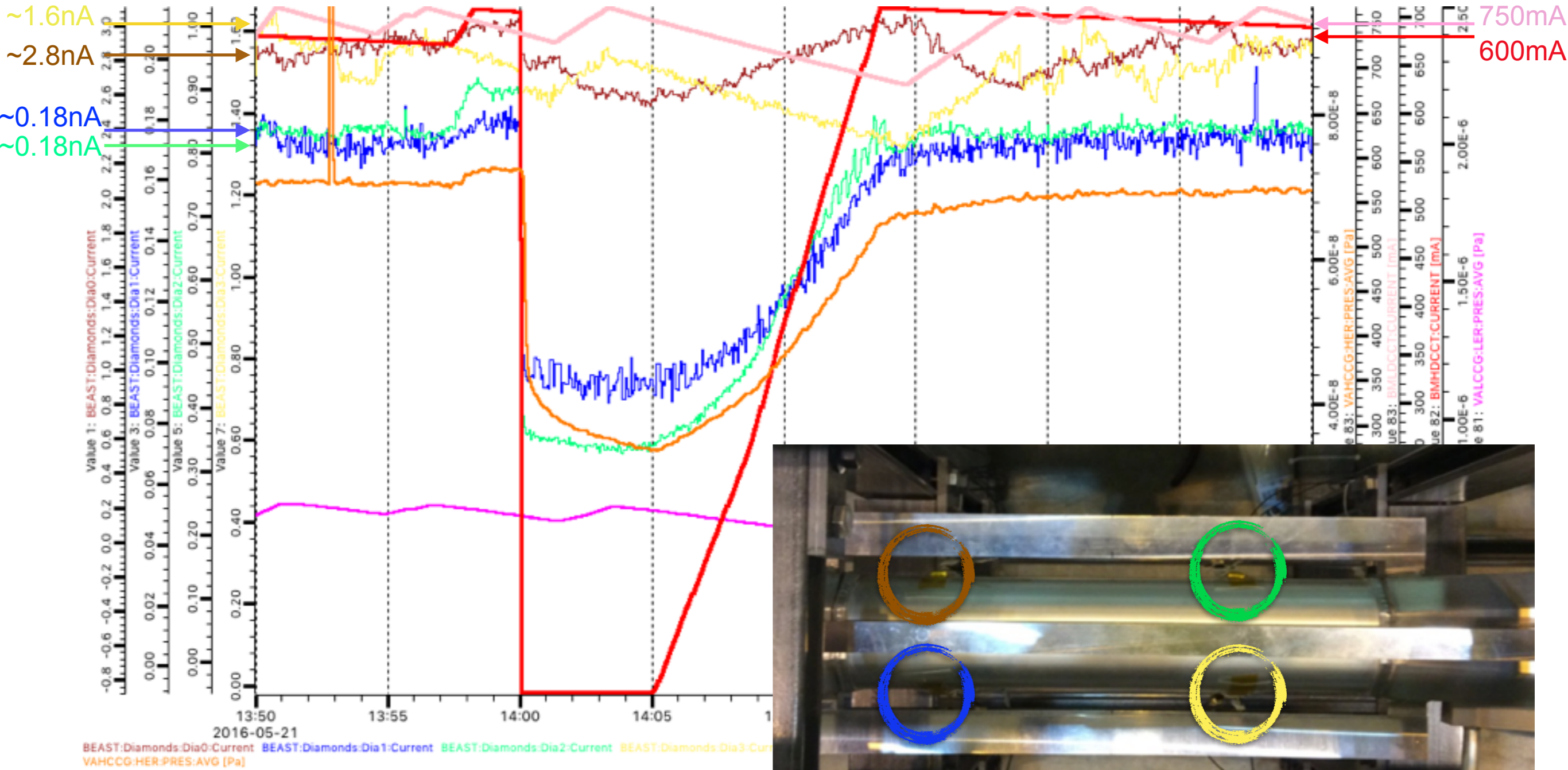
- shallow traps
- deep traps

τ_s → time constant associated to shallow traps

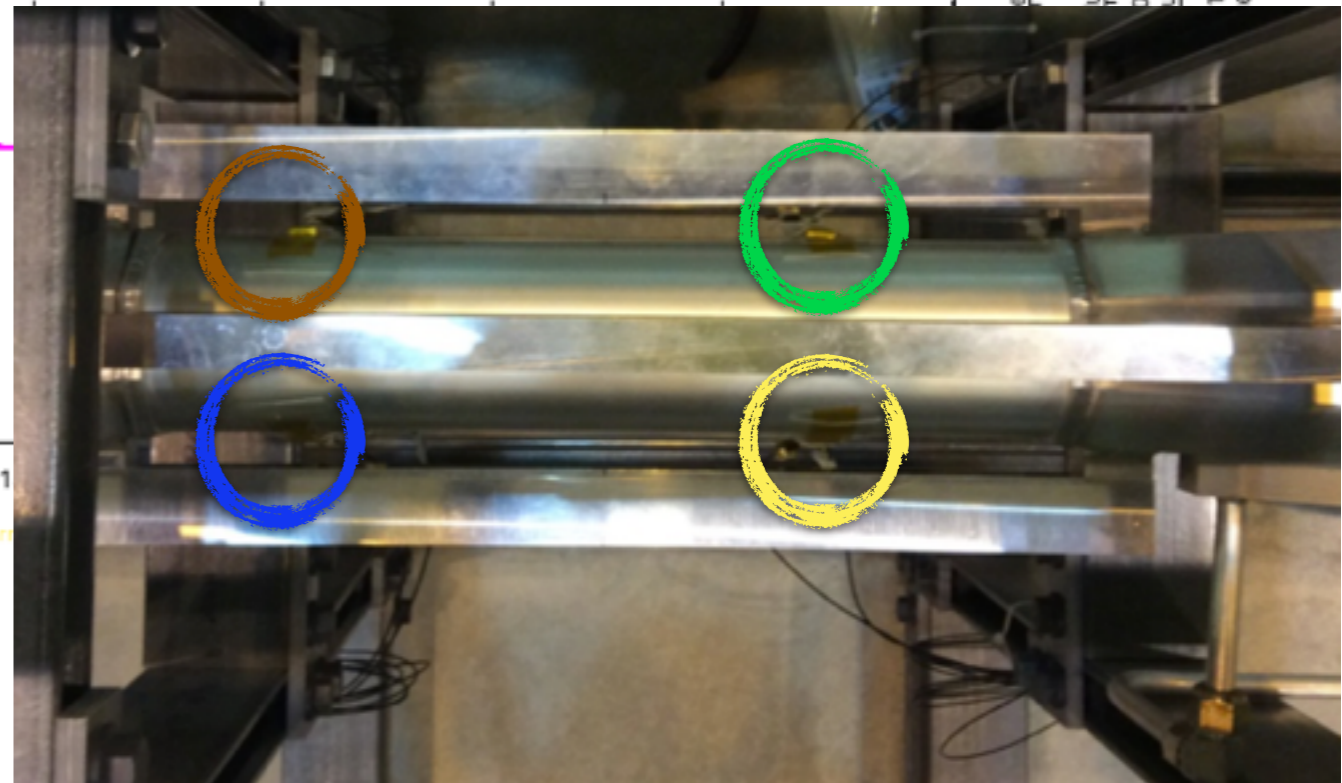
τ_d → time constant associated to deep traps

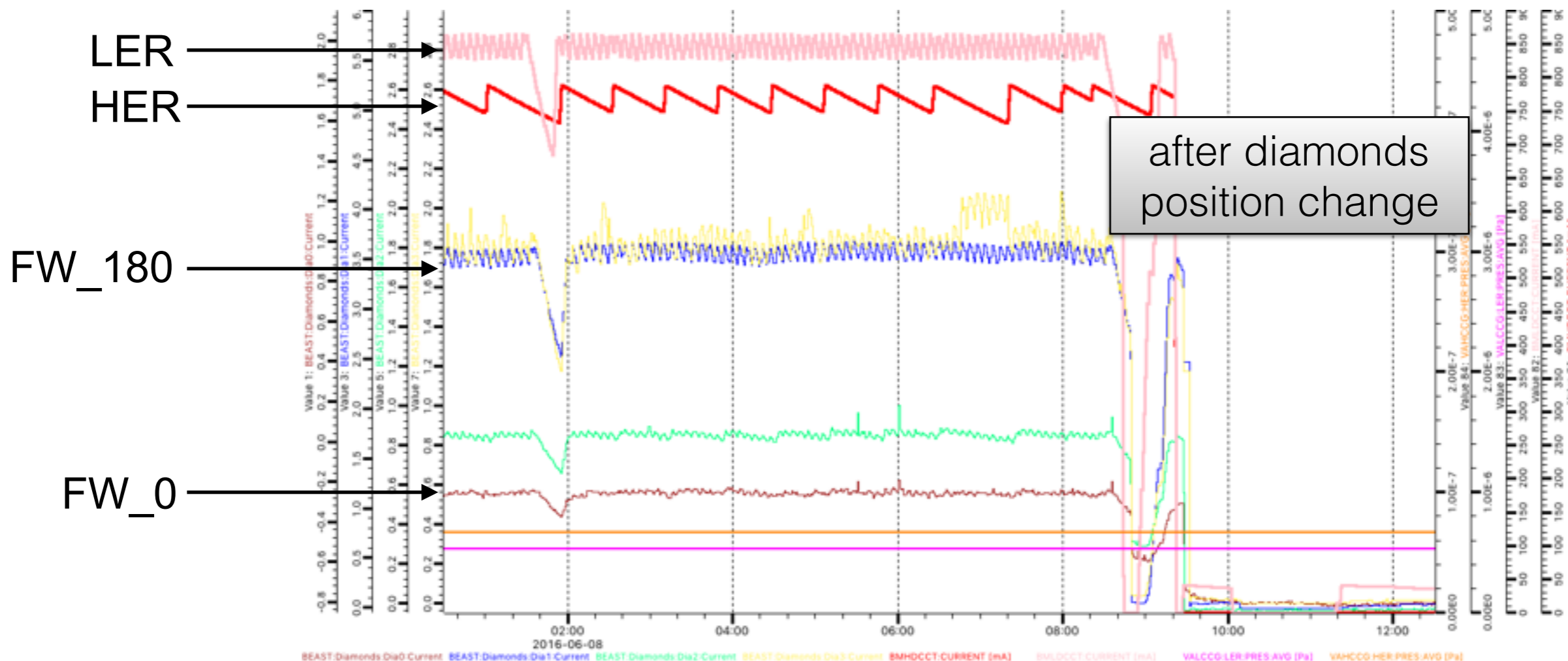
inferred from the fit

Diamond sensor response



- HER beam current
- LER beam current





before diamonds position change:

$I_{HER} \sim 700 \text{ mA}$ $I_{LER} \sim 750 \text{ mA}$

$I_{FW_0} \sim 0.16 \text{ nA (DC3)}$

$I_{FW_180} \sim 2.6 \text{ nA (DM7)}$

DM7 ↔ DC3

after diamonds position change:

$I_{HER} \sim 750 \text{ mA}$ $I_{LER} \sim 850 \text{ mA}$

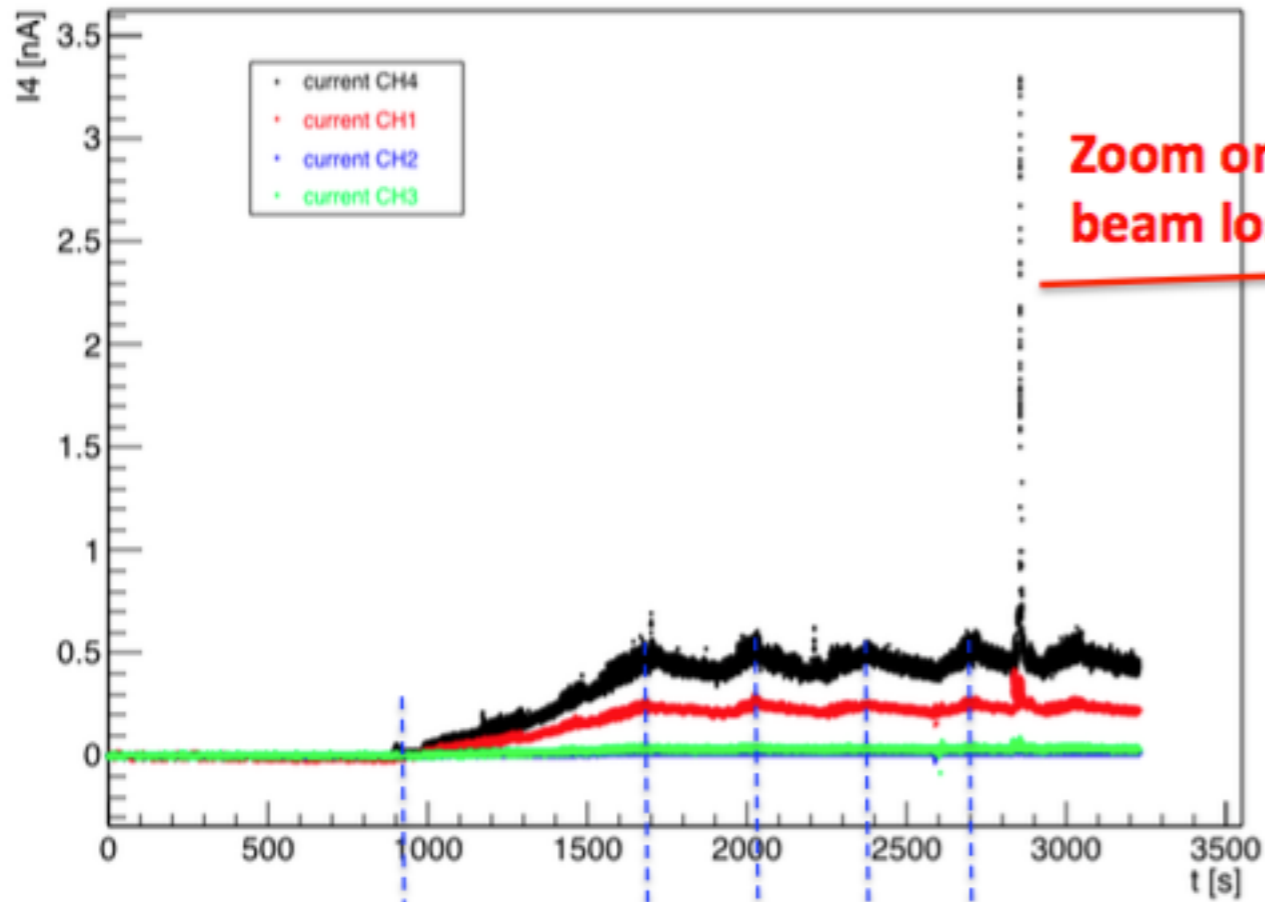
$I_{FW_0} \sim 0.4 \text{ nA (DM7)}$

$I_{FW_180} \sim 3.5 \text{ nA (DC3)}$

Diamonds currents well correlated to their position on the beam pipe

First signals

Currents vs time

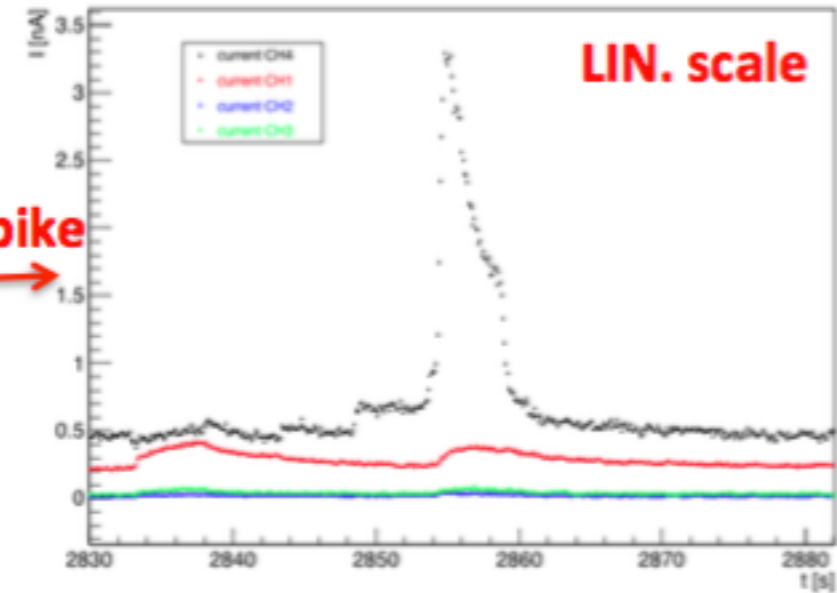


Start filling

Top-off every 4 min.

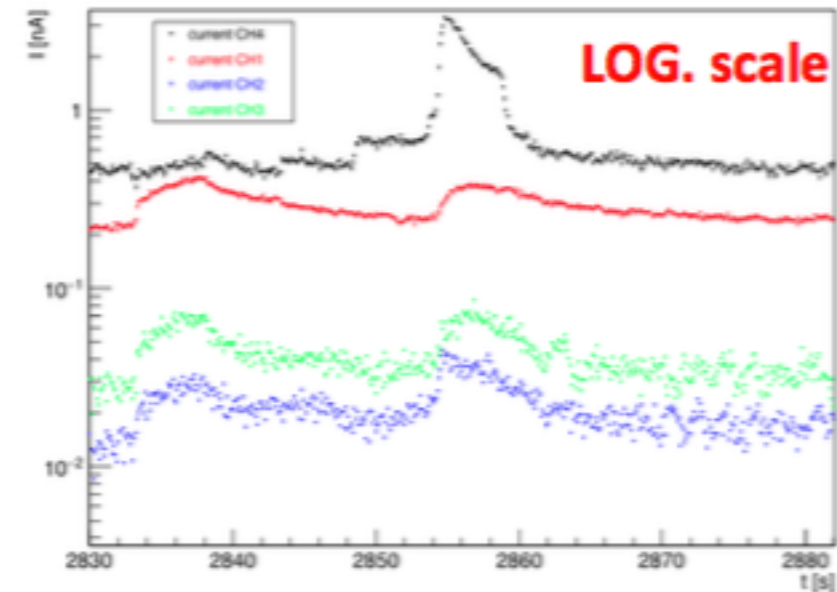
Zoom on beam loss spike

Currents vs time



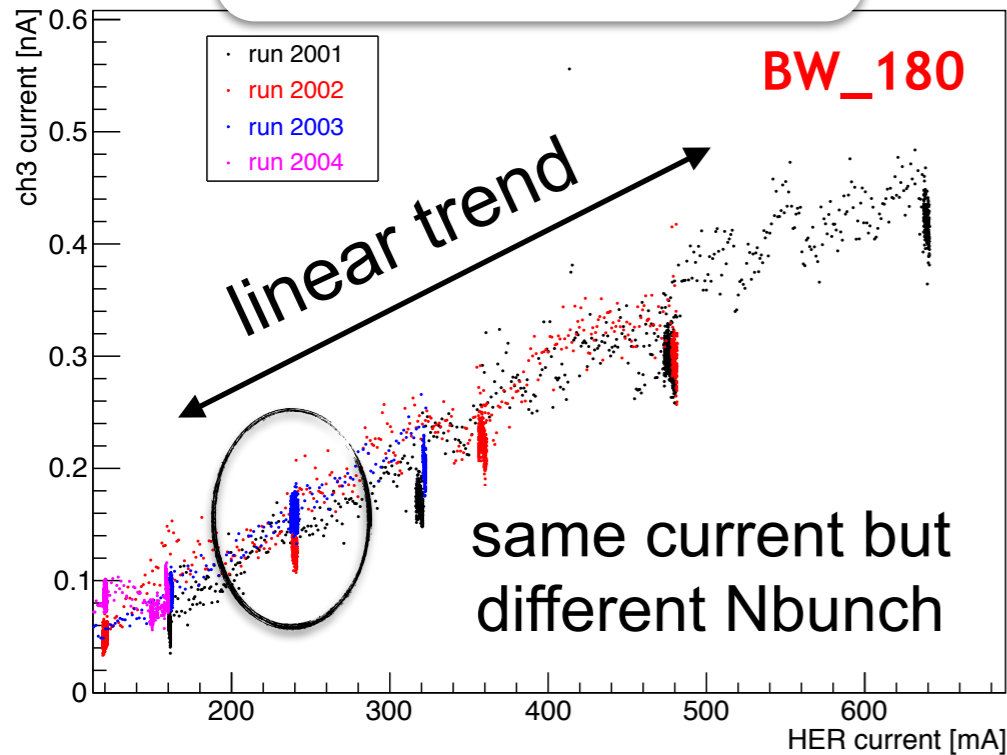
LIN. scale

Currents vs time

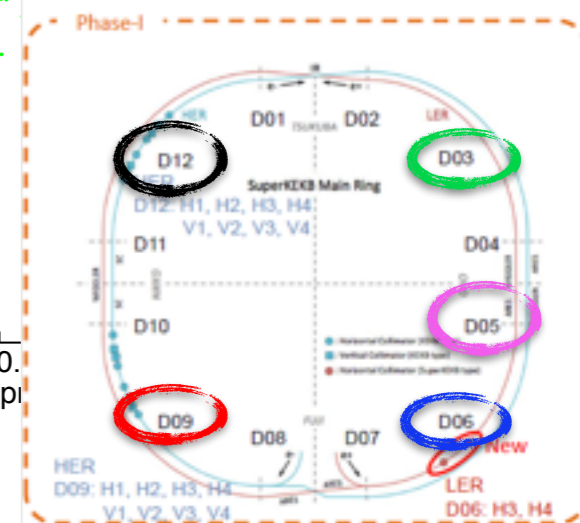
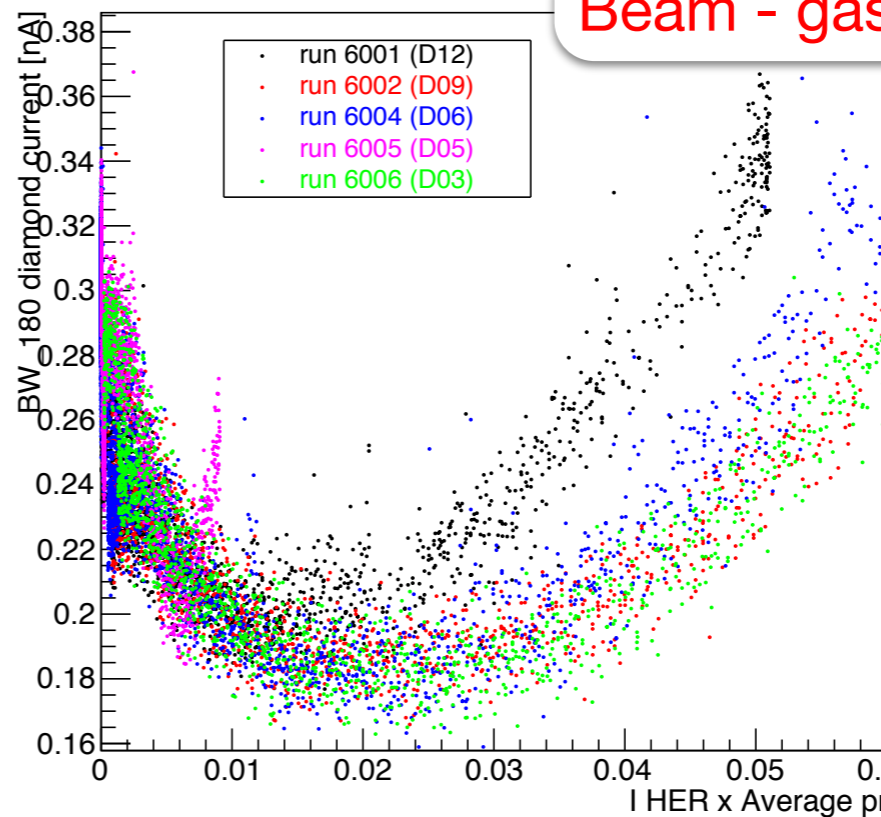


LOG. scale

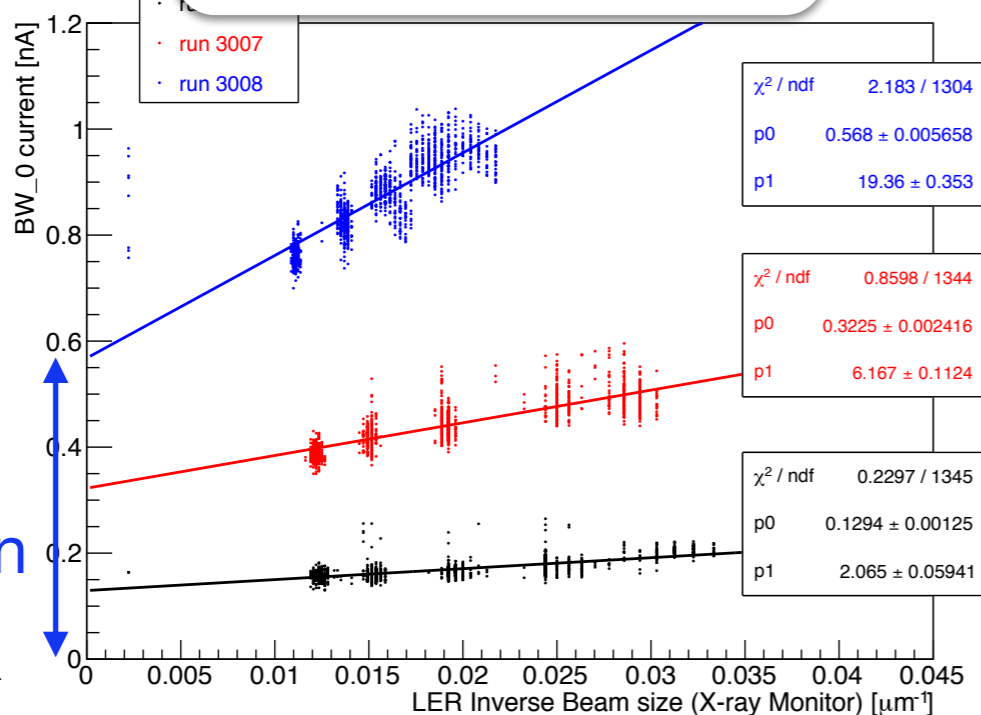
Current scan



Beam - gas scattering



Touschek scattering



Diamond current vs inverse beam size:
 Linear fit, intercept
 → extrapolation to pure beam-gas contribution

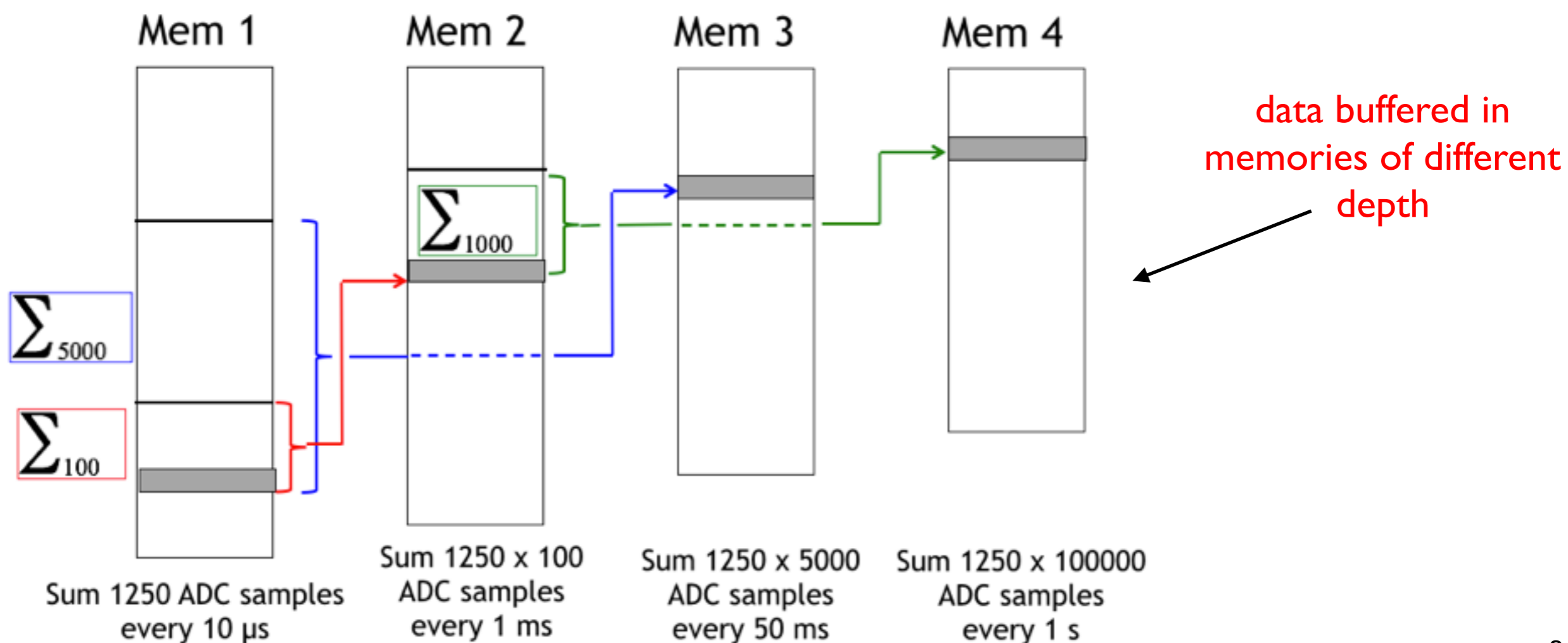
Beam abort thresholds (1/2)

Preliminary study from diamond sensors

Diamonds: Abort Buffer Memories

- diamond current will be sampled and digitized at 100kHz
- several levels of running averages are computed providing an effective digital filter

Present configuration of revolving Abort Buffer Memories to be improved with really “running sums”



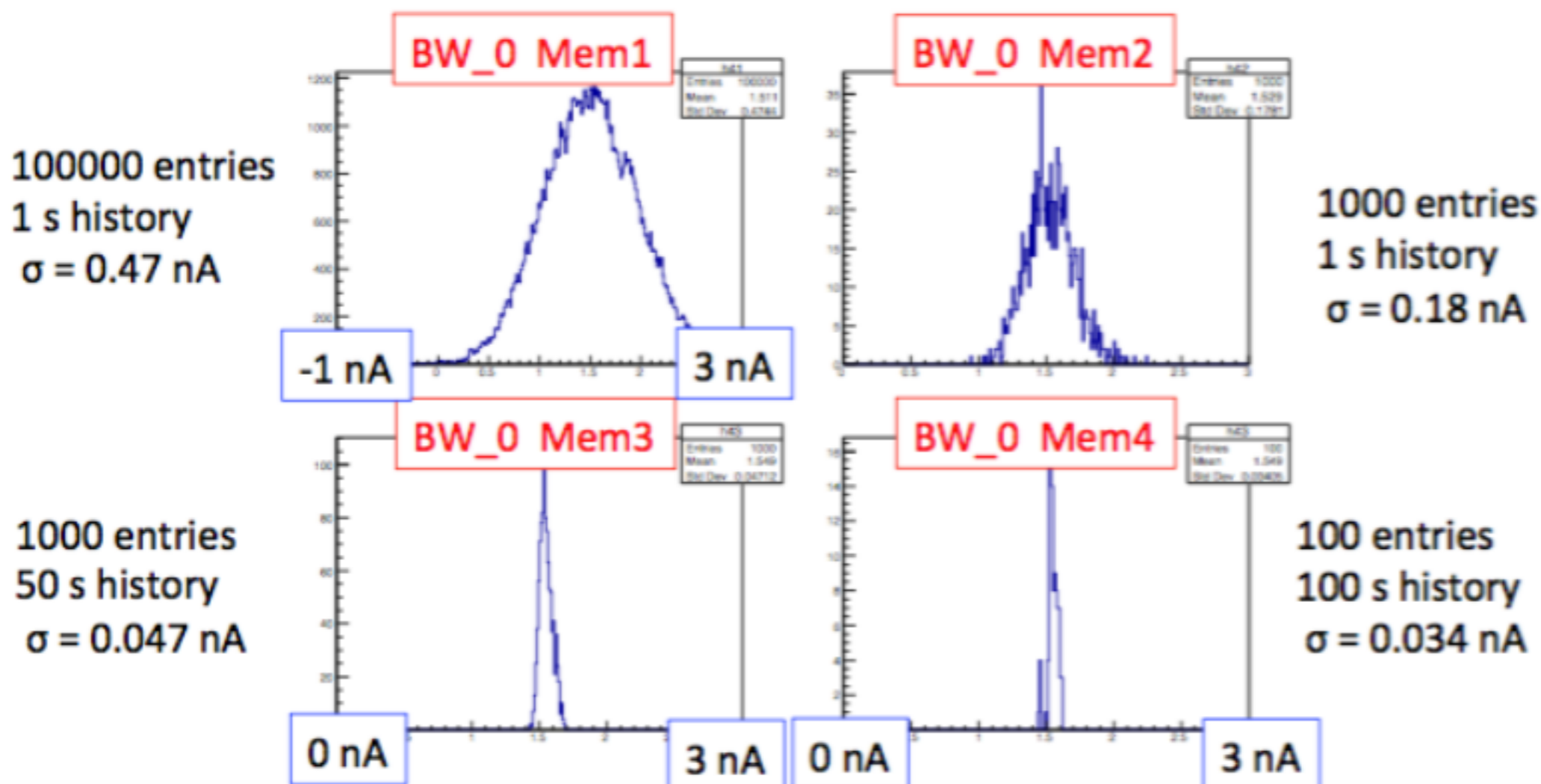
Beam abort thresholds (2/2)

Buffer memories: snapshot example

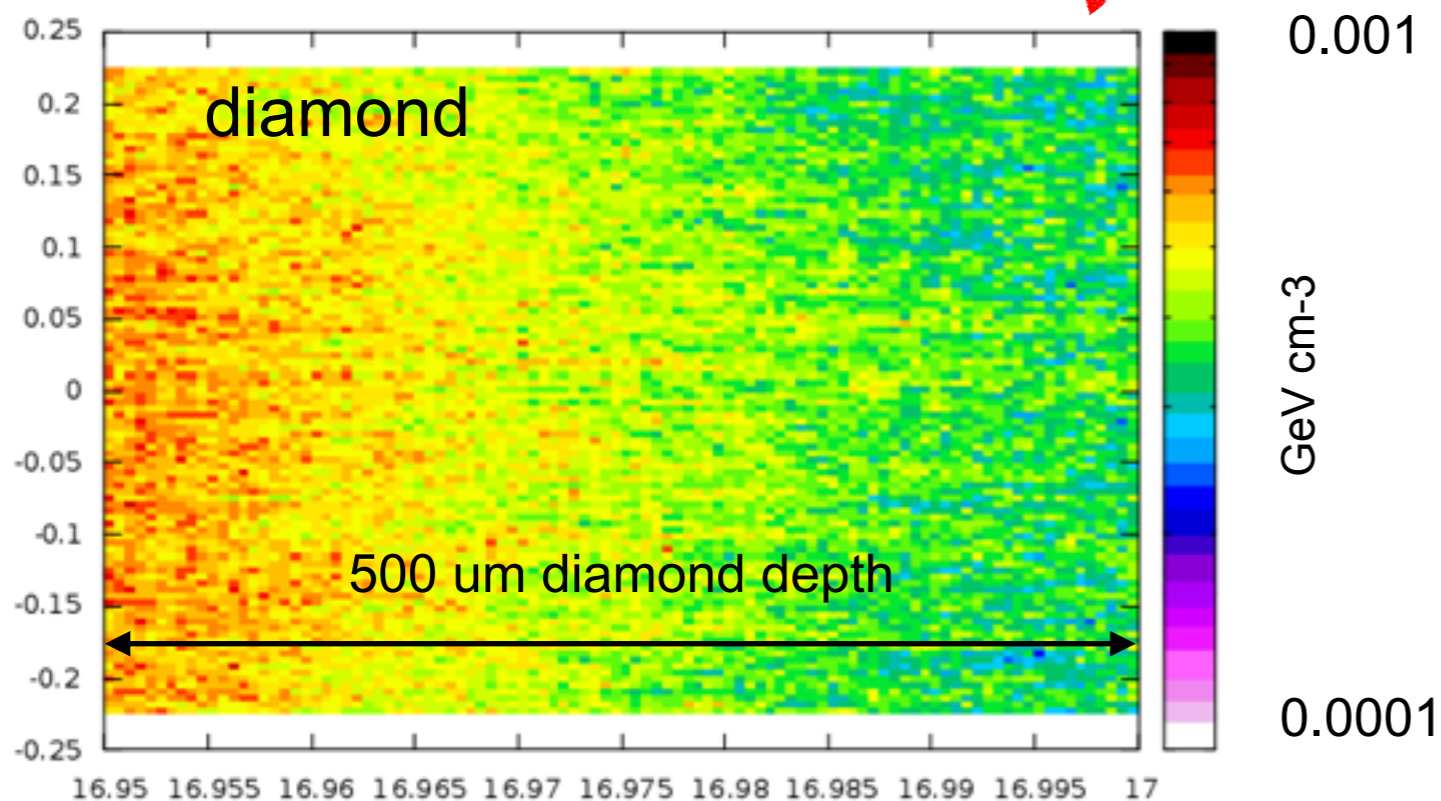
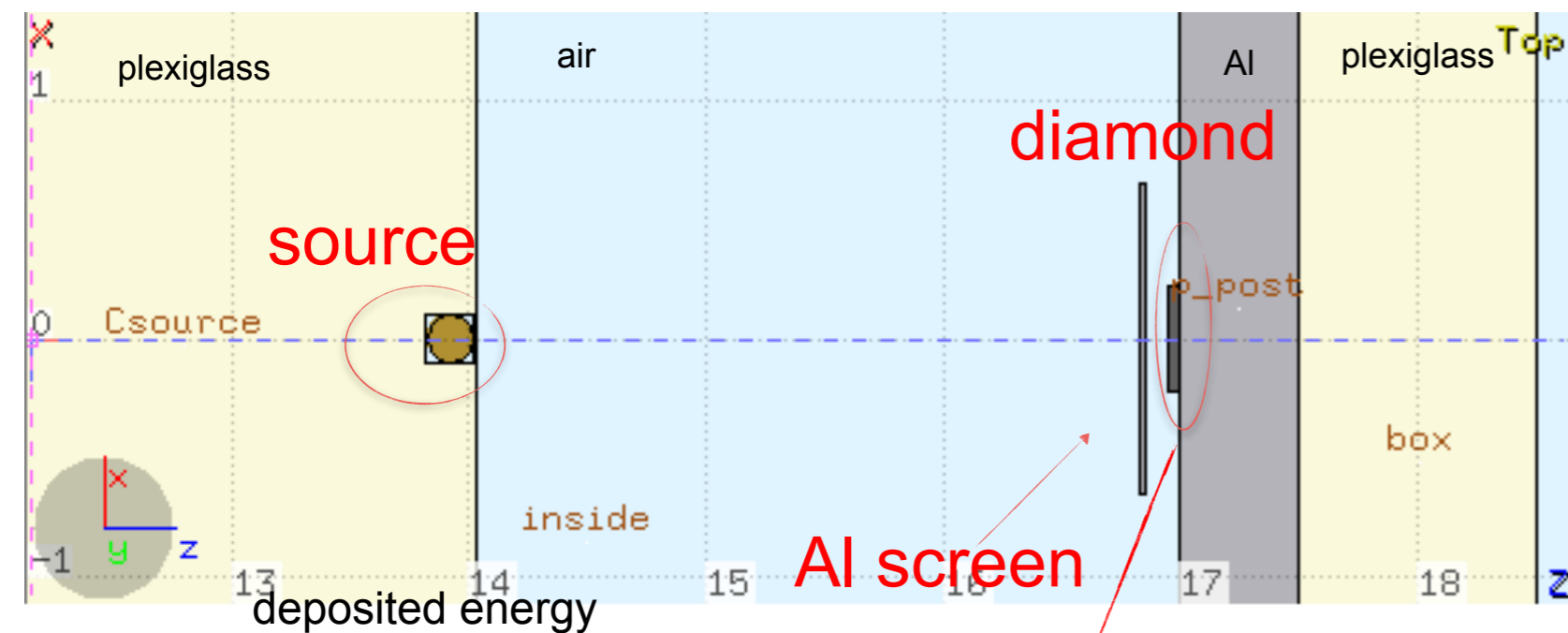
Example of snapshot of Buffer Memories (Mem1 to Mem4) for Dia3 = BW_0 in stable beam conditions, with average $I(\text{BW}_0) = 1.5 \text{ nA}$

Noise decreases with increased averaging, from about 0.47 nA to $< 0.04 \text{ nA}$

OK both for fast ($10 \mu\text{s}$) and slow ($> 1 \text{ s}$) beam aborts with appropriate thresholds



simplified geometry:

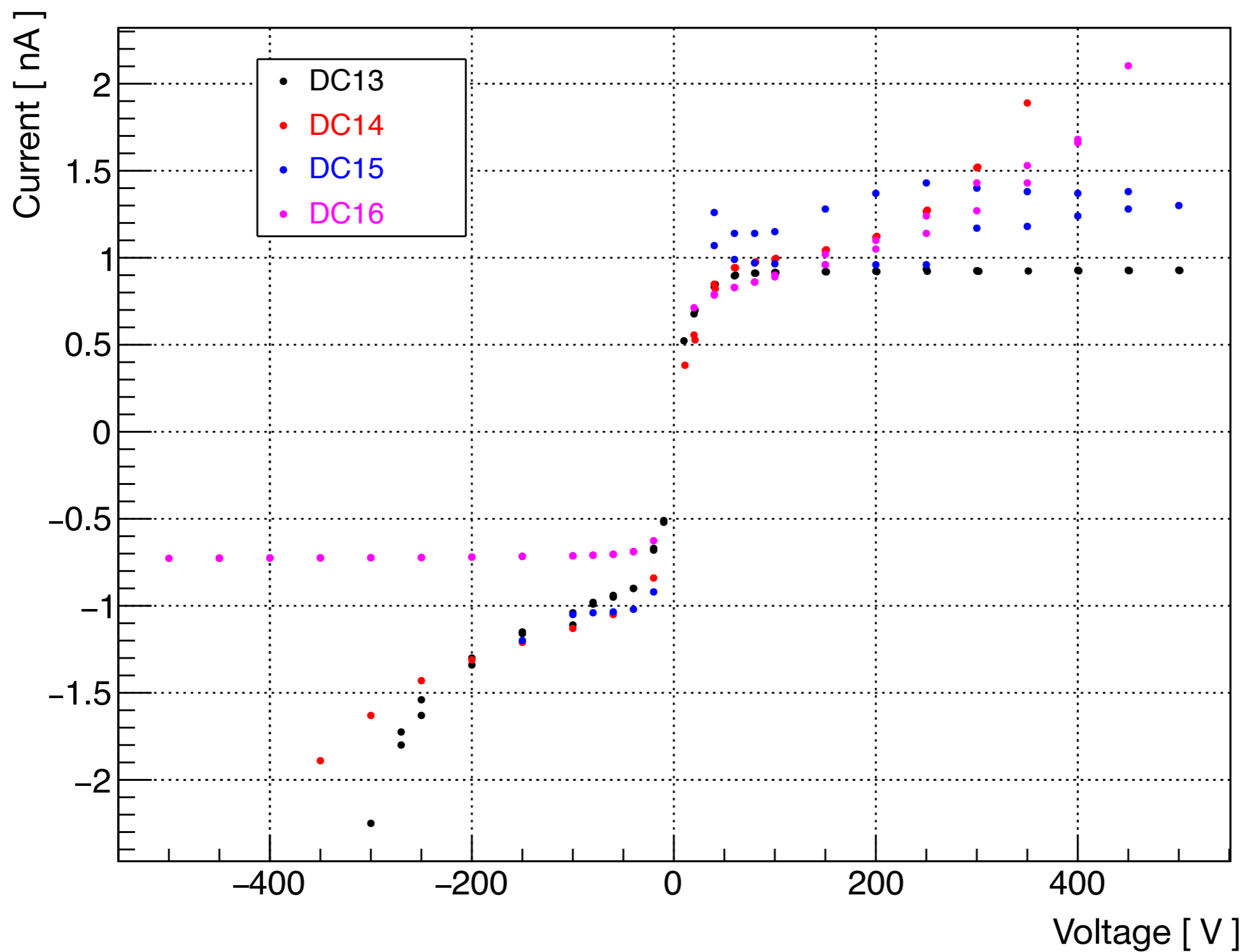


$$\text{photoconductive gain} = I_{\text{meas}}/I_{\text{FLUKA}}$$

assuming:

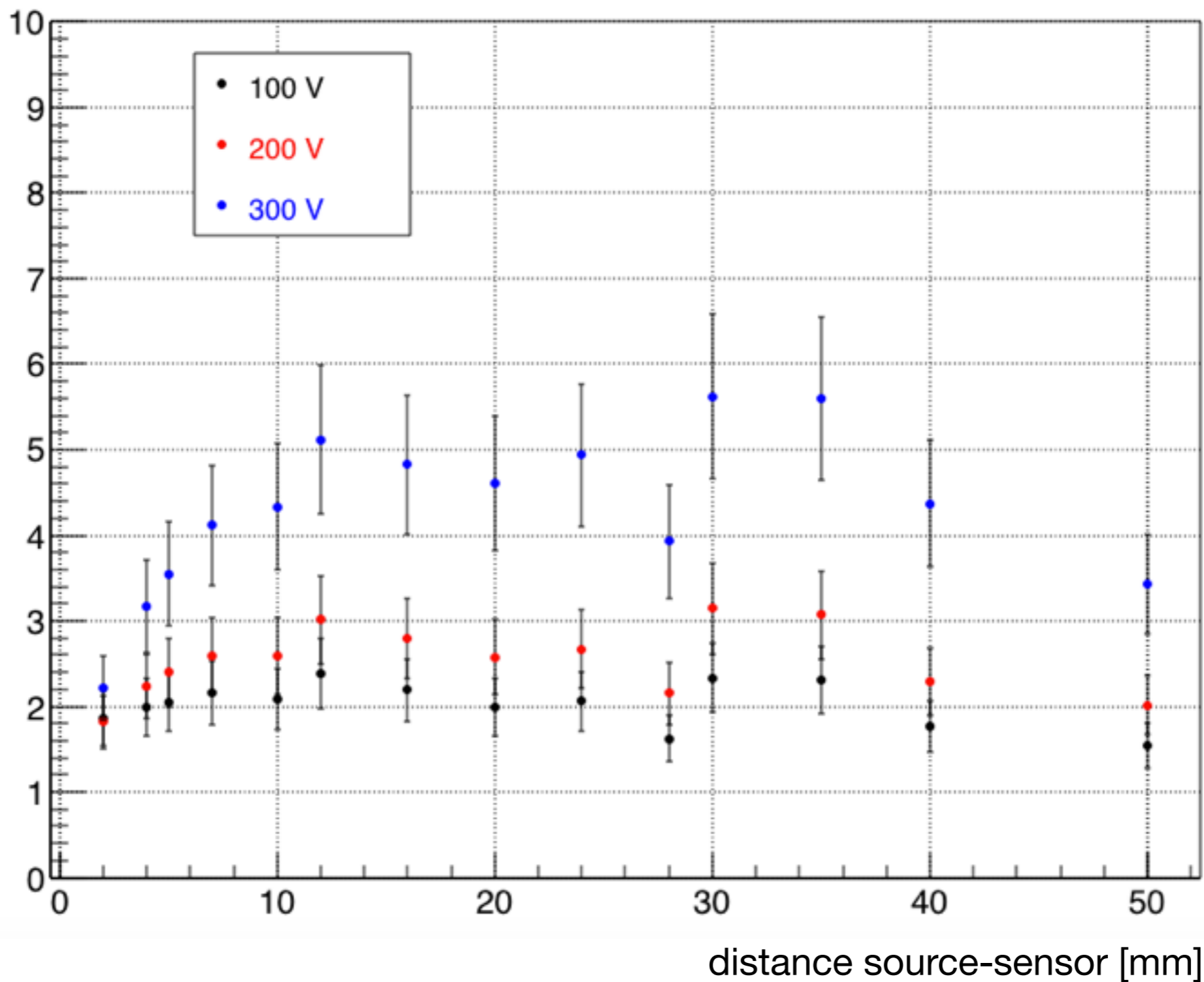
- deposited energy equal in simulation and measurement
- $CCE_{\text{FLUKA}} = 1, CCE_{\text{meas}} = 1$
- no photoconductive gain in simulation

IV characteristic



Photoconductive gain

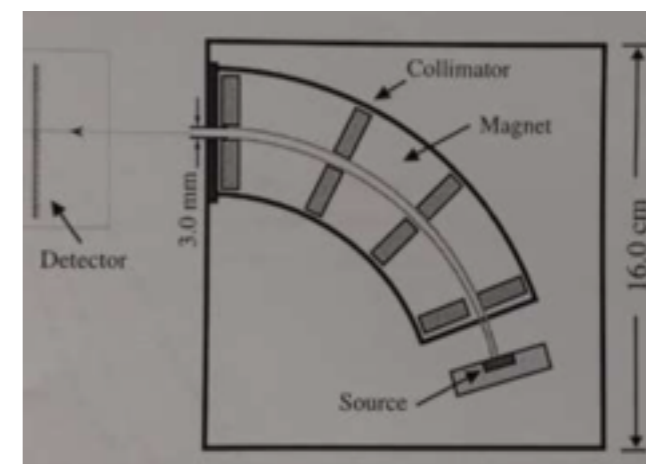
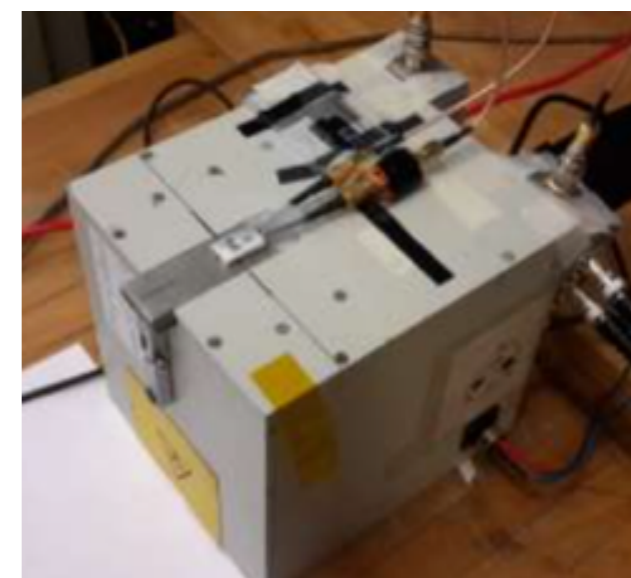
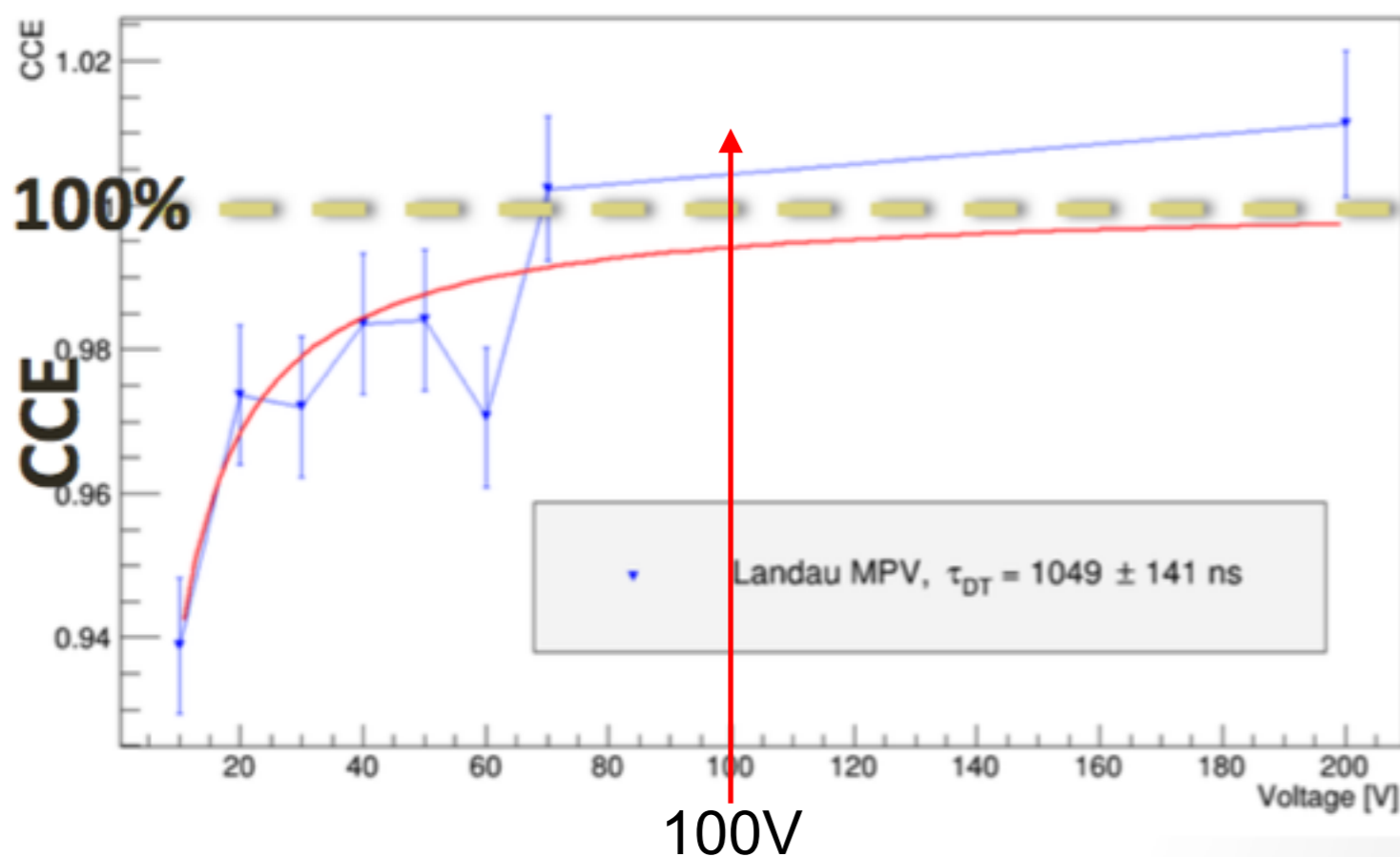
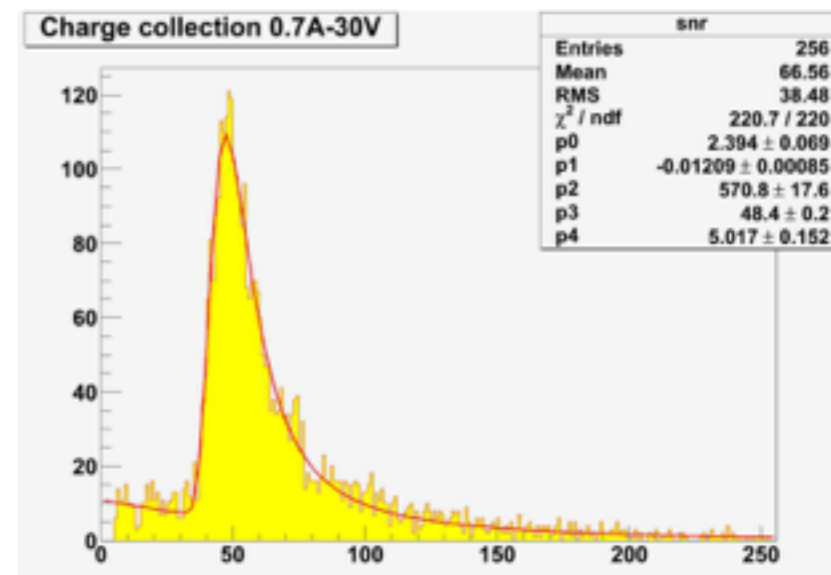
Gain factor



Example: DM5, CCE \approx 100%

Landau Most Probable Value (MPV) vs HV \rightarrow Charge Collection Efficiency

$$CCE = \frac{Q_{raccolta}}{Q_{generata}} = \frac{v_{dr}\tau}{d} \left(1 - e^{-\frac{d}{v_{dr}\tau}} \right), \text{ con } v_{dr} = \mu \frac{V}{d}$$



Current-dose calibration factor (1/2)

Reference: With β ^{90}Sr source at 18 mm distance \rightarrow FLUKA vs measurement
We measure currents \rightarrow we need a conversion factor from current to dose

FLUKA

- RE (Released Energy) = 3.25 GeV/s

- Assuming:

- $\text{CCE}_{\text{FLUKA}} = 1$
- $E_{e-h} = 13 \text{ eV}$

predicted current

$$I_{\text{FLUKA}} = \frac{\text{RE}_{\text{FLUKA}} * q_e}{E_{e-h}}$$

generated charge

$$\text{CCE}_{\text{FLUKA}} * (\text{GPC})_{\text{FLUKA}} = 40 \text{ pA}$$

$$\text{Dose} = \frac{\text{RE} * 1.6 \cdot 10^{-19}}{M} = 1.47 \text{ mrad/s}$$

predicted dose rate

$$(\text{Dose}/I) = \frac{1.47 \text{ mrad/s}}{0.04 \text{ nA}} = \frac{37 \text{ mrad/s}}{\text{nA}}$$

dose - current conversion factor

Current-dose calibration factor (2/2)

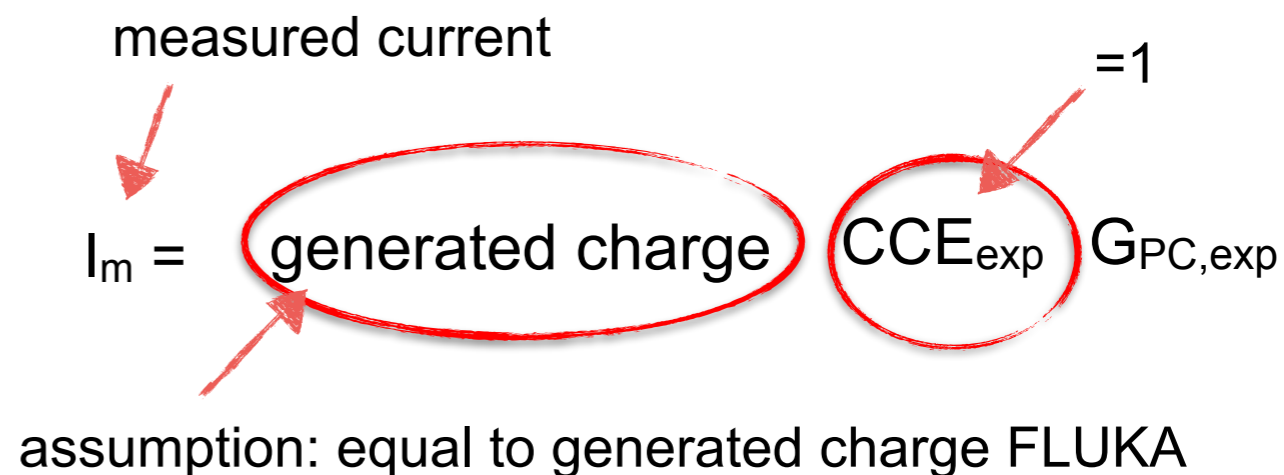
We measure currents -> we need a conversion factor from current to dose

Measurements

Photoconductive gain = I_m / I_{FLUKA}

I(pA)	@-100V	@+100 V
Fluka*	-40	+40
DM4	-850	+660
DM5	-460	+180
DC3	-230	+340
DM7*	-130	+340

G_{PC-}	G_{PC+}
21.25	16.5
11.5	4.5
5.75	8.5
3.25	8.5



$$\text{Dose (mrad/s)} = \frac{I_m \text{ (nA)} * 37 \text{ mrad/s/nA}}{G_{PC}}$$

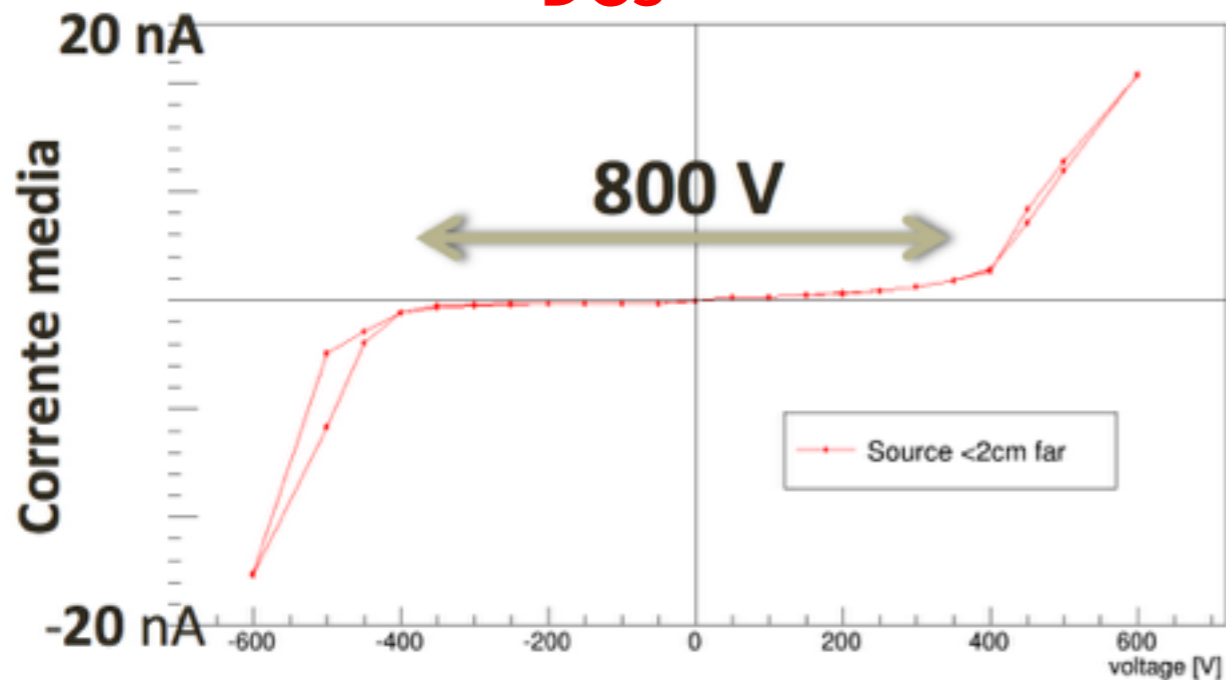
DOSE RATE

Systematics

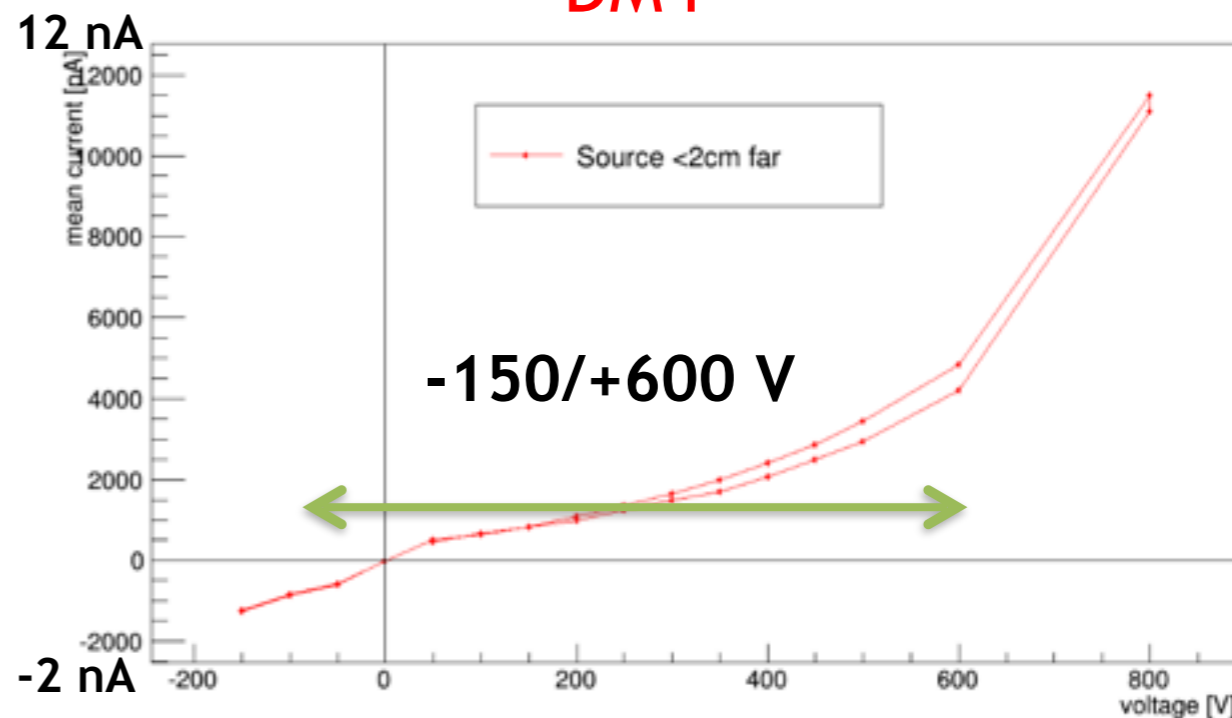
- Source distance -> 11%
- Diamond Active Volume-> 10%
- Source activity -> 7%
- Electronics Offset drift ~ 2%
- HV effects order 1%
- Priming/pumping effects (initial stability)<10% (long term < 1%)
- FLUKA simulation -> 1 %

I-V with β ^{90}Sr source (d=18mm)

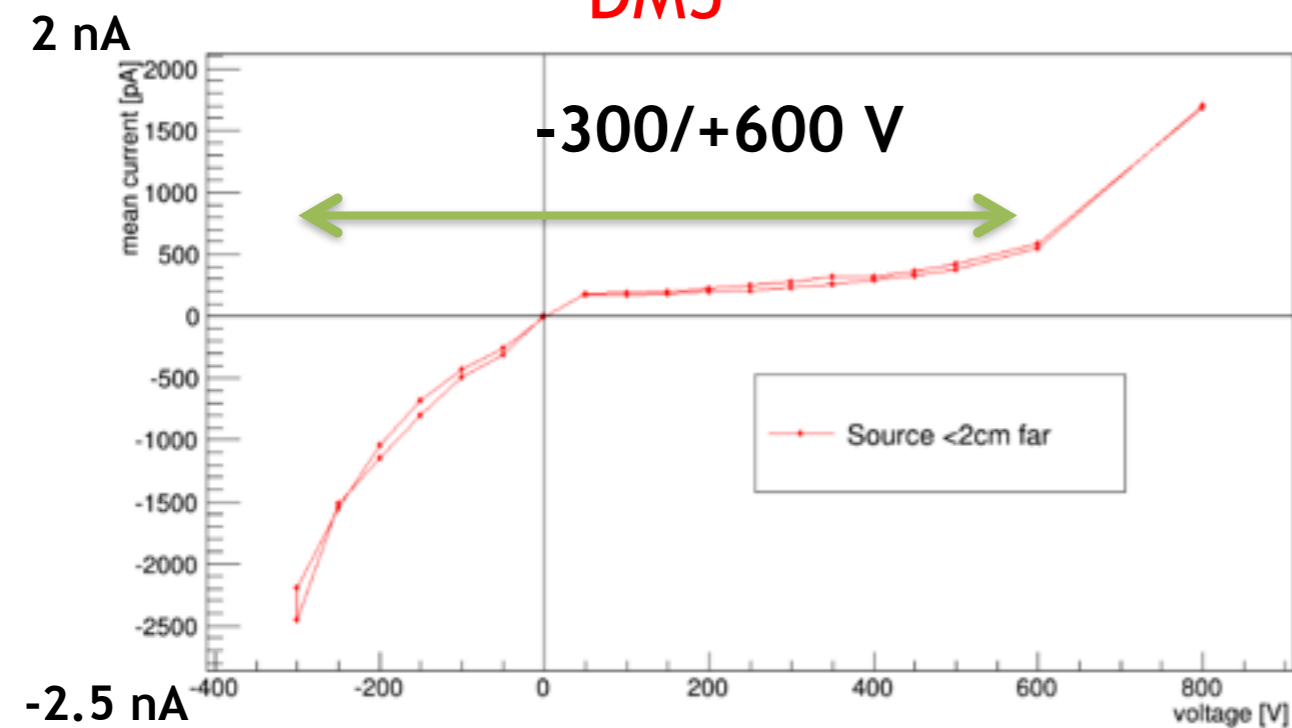
DC3



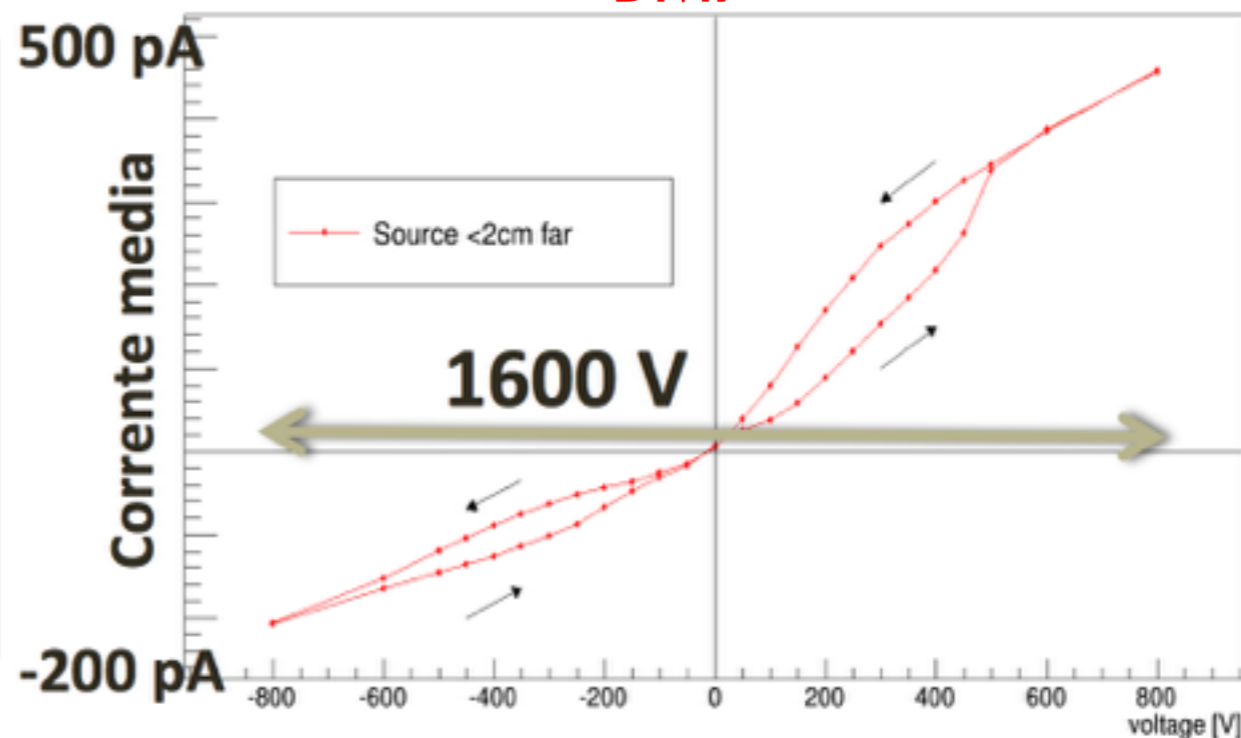
DM4



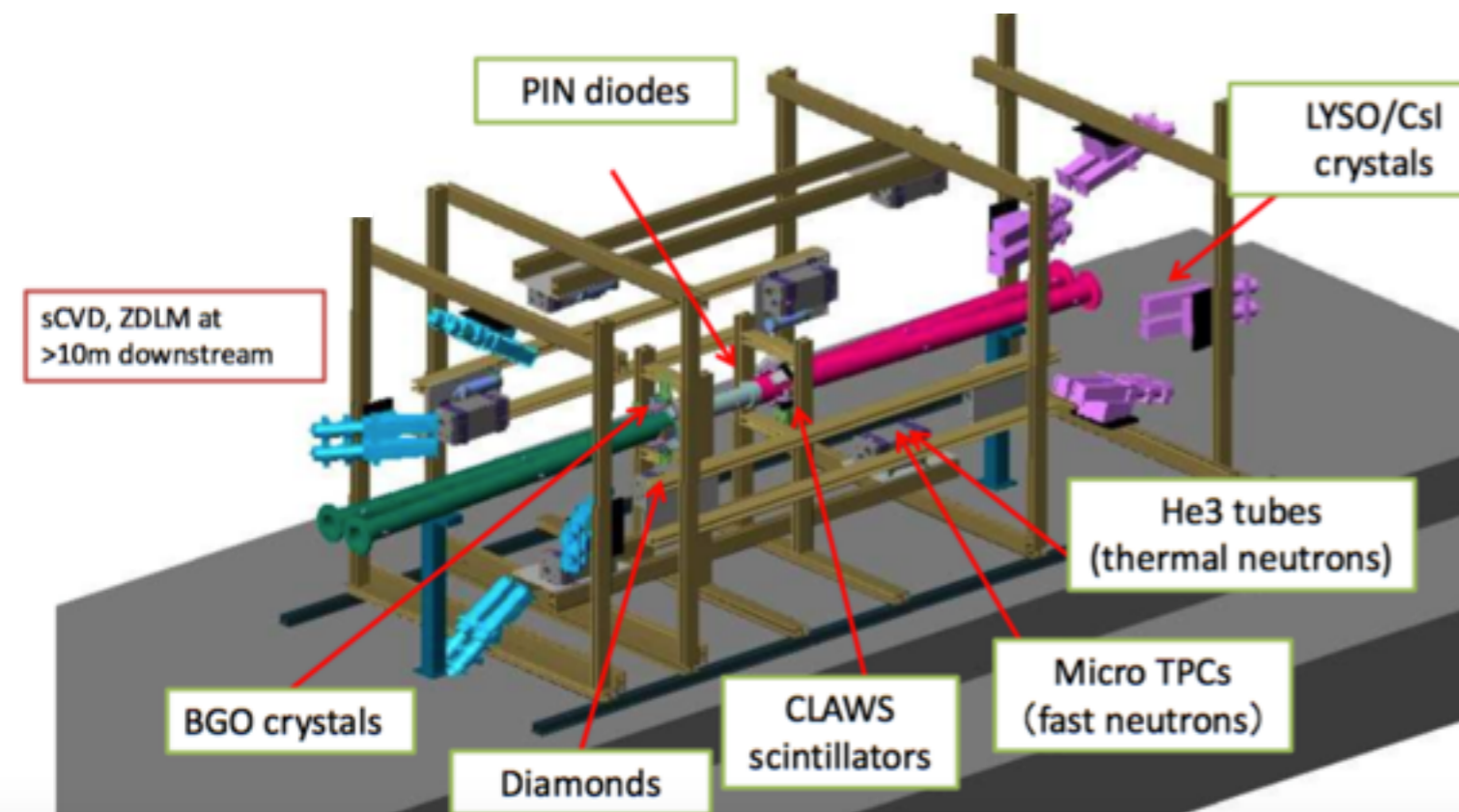
DM5



DM7



BEAST sensors



System	Detectors installed	Measurement
“CLAWS” scintillator	8	injection backgrounds
Diamonds	4	ionization dose
BGO	8	luminosity
Crystals	6 CsI(Tl) 6 CsI 6 LYSO	EM energy spectrum
He-3 tubes	4	thermal neutron flux
Micro-TPCs	2	fast neutron
PIN diodes	64	neutral vs charged radiation dose